

# Marius Grundmann

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

741 papers	25,684 citations	74 h-index	136 g-index
804 ext. papers	27,795 ext. citations	3.1 avg, IF	6.97 L-index

#	Paper	IF	Citations
741	Epitaxial lift-off of single crystalline CuI thin films. <i>Journal of Materials Chemistry C</i> , <b>2022</b> , 10, 4124-4127	7.1	
740	Al Composition Dependence of Band Offsets for SiO <sub>2</sub> on $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ . <i>ECS Journal of Solid State Science and Technology</i> , <b>2021</b> , 10, 113007	2	1
739	All-Amorphous Junction Field-Effect Transistors Based on High-Mobility Zinc Oxynitride. <i>Advanced Electronic Materials</i> , <b>2021</b> , 7, 2000883	6.4	1
738	Transient birefringence and dichroism in ZnO studied with fs-time-resolved spectroscopic ellipsometry. <i>Physical Review Research</i> , <b>2021</b> , 3,	3.9	2
737	Progression of group-III sesquioxides: epitaxy, solubility and desorption. <i>Journal Physics D: Applied Physics</i> , <b>2021</b> , 54, 223001	3	7
736	Hot-phonon effects in photo-excited wide-bandgap semiconductors. <i>Journal of Physics Condensed Matter</i> , <b>2021</b> , 33,	1.8	1
735	Numerical Modeling of Schottky Barrier Diode Characteristics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2021</b> , 218, 2100121	1.6	
734	Evidence for oxygen being a dominant shallow acceptor in p-type CuI. <i>APL Materials</i> , <b>2021</b> , 9, 051101	5.7	3
733	p-Type Doping and Alloying of CuI Thin Films with Selenium. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2021</b> , 15, 2100214	2.5	2
732	Azimuthal Anisotropy of Rhombohedral (Corundum Phase) Heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 2100104	1.3	3
731	Structural and Elastic Properties of $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ Thin Films on (11.0) Al <sub>2</sub> O <sub>3</sub> Substrates for the Entire Composition Range. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 2000394	1.3	9
730	Control of Optical Absorption and Emission of Sputtered Copper Iodide Thin Films. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2021</b> , 15, 2000431	2.5	3
729	Epitaxial Growth of $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ Layers and Superlattice Heterostructures up to $x = 0.48$ on Highly Conductive Al-Doped ZnO Thin-Film Templates by Pulsed Laser Deposition. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 2000359	1.3	1
728	The Physics of Semiconductors. <i>Graduate Texts in Physics</i> , <b>2021</b> ,	0.3	5
727	Plastic strain relaxation and alloy instability in epitaxial corundum-phase (Al,Ga) <sub>2</sub> O <sub>3</sub> thin films on r-plane Al <sub>2</sub> O <sub>3</sub> . <i>Materials Advances</i> , <b>2021</b> , 2, 4316-4322	3.3	1
726	Indium Gallium Oxide Alloys: Electronic Structure, Optical Gap, Surface Space Charge, and Chemical Trends within Common-Cation Semiconductors. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2021</b> , 13, 2807-2819	8.5	13
725	Tuning material properties of amorphous zinc oxynitride thin films by magnesium addition. <i>APL Materials</i> , <b>2021</b> , 9, 021120	5.7	0

724	Fermi level controlled point defect balance in ion irradiated indium oxide. <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 085703	2.5	2
723	Epitaxial Zn <sub>3</sub> N <sub>2</sub> thin films by molecular beam epitaxy: Structural, electrical, and optical properties. <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 065104	2.5	0
722	Realization of highly rectifying Schottky barrier diodes and pn heterojunctions on $\alpha$ -Ga <sub>2</sub> O <sub>3</sub> by overcoming the conductivity anisotropy. <i>Journal of Applied Physics</i> , <b>2021</b> , 130, 084502	2.5	4
721	Strong coupling of Bloch surface waves and excitons in ZnO up to 430 K. <i>New Journal of Physics</i> , <b>2021</b> , 23, 093031	2.9	1
720	Epitaxial growth of rhombohedral $\beta$ - and cubic $\beta$ -CuI. <i>Journal of Crystal Growth</i> , <b>2021</b> , 570, 126218	1.6	3
719	Raman tensor determination of transparent uniaxial crystals and their thin films—plane GaN as exemplary case. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 121109	3.4	
718	Dynamics of exciton-polariton emission in CuI. <i>APL Materials</i> , <b>2021</b> , 9, 121102	5.7	2
717	Oxid-Halbleiter mit ultrabreiter Bandlücke. <i>Vakuum in Forschung Und Praxis</i> , <b>2020</b> , 32, 32-37	0.3	
716	Hybrid GA-gradient method for thin films ellipsometric data evaluation. <i>Journal of Computational Science</i> , <b>2020</b> , 47, 101201	3.4	1
715	Control of magnetic properties in spinel ZnFe <sub>2</sub> O <sub>4</sub> thin films through intrinsic defect manipulation. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 165702	2.5	4
714	Controlled formation of Schottky diodes on n-doped ZnO layers by deposition of p-conductive polymer layers with oxidative chemical vapor deposition. <i>Nano Express</i> , <b>2020</b> , 1, 010013	2	5
713	Dielectric function decomposition by dipole interaction distribution: application to triclinic K <sub>2</sub> Cr <sub>2</sub> O <sub>7</sub> . <i>New Journal of Physics</i> , <b>2020</b> , 22, 073041	2.9	0
712	Annealing Effects on the Band Alignment of ALD SiO <sub>2</sub> on (In <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> for x = 0.25–0.74. <i>ECS Journal of Solid State Science and Technology</i> , <b>2020</b> , 9, 045001	2	
711	Metal-Semiconductor Field-Effect Transistors Based on the Amorphous Multi-Anion Compound ZnON. <i>Advanced Electronic Materials</i> , <b>2020</b> , 6, 1901066	6.4	5
710	Changes in band alignment during annealing at 600 °C of ALD Al <sub>2</sub> O <sub>3</sub> on (In <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> for x = 0.25–0.74. <i>Journal of Applied Physics</i> , <b>2020</b> , 127, 105701	2.5	3
709	Low voltage, high gain inverters based on amorphous zinc tin oxide on flexible substrates. <i>APL Materials</i> , <b>2020</b> , 8, 061112	5.7	8
708	Solubility limit and material properties of a $\beta$ -(Al <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> thin film with a lateral cation gradient on (00.1)Al <sub>2</sub> O <sub>3</sub> by tin-assisted PLD. <i>APL Materials</i> , <b>2020</b> , 8, 021103	5.7	17
707	A Review of the Segmented-Target Approach to Combinatorial Material Synthesis by Pulsed-Laser Deposition. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900626	1.3	14

706	Anisotropic strain relaxation through prismatic and basal slip in $(\text{Al}, \text{Ga})\text{O}_3$ on R-plane $\text{Al}_2\text{O}_3$ . <i>APL Materials</i> , <b>2020</b> , 8, 021108	5.7	15
705	Magnetic Anisotropy in Thin Layers of $(\text{Mn}, \text{Zn})\text{Fe}_2\text{O}_4$ on $\text{SrTiO}_3$ (001). <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900627	1.3	1
704	Band Offsets at $(\text{Al}, \text{In})\text{GaO}/\text{MgO}$ Interfaces. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2020</b> , 12, 8879-8885	3.5	12
703	Universal relation for the orientation of dislocations from prismatic slip systems in hexagonal and rhombohedral strained heterostructures. <i>Applied Physics Letters</i> , <b>2020</b> , 116, 082104	3.4	5
702	Nickel vacancy acceptor in nickel oxide: Doping beyond thermodynamic equilibrium. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	8
701	Dielectric tensor, optical activity, and singular optic axes of KTP in the spectral range 0.58.4 eV. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	1
700	Investigating the ranges of (meta)stable phase formation in $(\text{In}_x\text{Ga}_{1-x})\text{O}_3$ : Impact of the cation coordination. <i>Physical Review Materials</i> , <b>2020</b> , 4,	3.2	4
699	Influence of the excitation conditions on the emission behavior of carbon nanodot-based planar microcavities. <i>Physical Review Research</i> , <b>2020</b> , 2,	3.9	2
698	Diodes 2. <i>Springer Series in Materials Science</i> , <b>2020</b> , 689-702	0.9	1
697	Enhanced Magnetoelectric Coupling in $\text{BaTiO}_3\text{-BiFeO}_3$ Multilayers-An Interface Effect. <i>Materials</i> , <b>2020</b> , 13,	3.5	8
696	Comment on "Stress-strain state in $\text{Ga}_2\text{O}_3$ epitaxial films on $\text{Al}_2\text{O}_3$ substrates" [Appl. Phys. Express 13, 075502 (2020)]. <i>Applied Physics Express</i> , <b>2020</b> , 13, 089101	2.4	1
695	Topological states of the diatomic linear chain: effect of impedance matching to the fixed ends. <i>New Journal of Physics</i> , <b>2020</b> , 22, 083076	2.9	
694	Identification of $\text{LiNi}$ and $\text{VNi}$ acceptor levels in doped nickel oxide. <i>APL Materials</i> , <b>2020</b> , 8, 121106	5.7	2
693	Pulsed Laser Deposition 2. <i>Springer Series in Materials Science</i> , <b>2020</b> , 273-291	0.9	4
692	Growth, structural and optical properties of coherent $(\text{Al}_x\text{Ga}_{1-x})\text{O}_3/\text{Ga}_2\text{O}_3$ quantum well superlattice heterostructures. <i>APL Materials</i> , <b>2020</b> , 8, 051112	5.7	11
691	Epitaxial growth and strain relaxation of corundum-phase $(\text{Al}, \text{Ga})\text{O}_3$ thin films from pulsed laser deposition at 1000 °C on r-plane $\text{Al}_2\text{O}_3$ . <i>Applied Physics Letters</i> , <b>2020</b> , 117, 242102	3.4	5
690	$\text{SnO}/\text{Ga}_2\text{O}_3$ vertical pn heterojunction diodes. <i>Applied Physics Letters</i> , <b>2020</b> , 117, 252106	3.4	14
689	Control of phase formation of $(\text{Al}_x\text{Ga}_{1-x})\text{O}_3$ thin films on c-plane $\text{Al}_2\text{O}_3$ . <i>Journal Physics D: Applied Physics</i> , <b>2020</b> , 53, 485105	3	13

688	Experimental exploration of the amphoteric defect model by cryogenic ion irradiation of a range of wide band gap oxide materials. <i>Journal of Physics Condensed Matter</i> , <b>2020</b> ,	1.8	4
687	Ultrafast dynamics of hot charge carriers in an oxide semiconductor probed by femtosecond spectroscopic ellipsometry. <i>New Journal of Physics</i> , <b>2020</b> , 22, 083066	2.9	10
686	Impact of Defects on Magnetic Properties of Spinel Zinc Ferrite Thin Films. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900630	1.3	7
685	Nickel OxideBased Heterostructures with Large Band Offsets. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 1900639	1.3	8
684	Ultrahigh-performance integrated inverters based on amorphous zinc tin oxide deposited at room temperature. <i>APL Materials</i> , <b>2020</b> , 8, 091111	5.7	3
683	Toward three-dimensional hybrid inorganic/organic optoelectronics based on GaN/oCVD-PEDOT structures. <i>Nature Communications</i> , <b>2020</b> , 11, 5092	17.4	6
682	High mobility, highly transparent, smooth, p-type CuI thin films grown by pulsed laser deposition. <i>APL Materials</i> , <b>2020</b> , 8, 091115	5.7	14
681	Topological States Due to Third-Neighbor Coupling in Diatomic Linear Elastic Chains. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 2000176	1.3	1
680	From energy harvesting to topologically insulating behavior: ABO <sub>3</sub> -type epitaxial thin films and superlattices. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 15575-15596	7.1	8
679	Controllable Growth of Copper Iodide for High-Mobility Thin Films and Self-Assembled Microcrystals. <i>ACS Applied Electronic Materials</i> , <b>2020</b> , 2, 3627-3632	4	4
678	Experimental evidence of wide bandgap in triclinic (001)-oriented Sn <sub>5</sub> O <sub>2</sub> (PO <sub>4</sub> ) <sub>2</sub> thin films on Y <sub>2</sub> O <sub>3</sub> buffered glass substrates. <i>Journal of Materials Chemistry C</i> , <b>2020</b> , 8, 14203-14207	7.1	1
677	All-Oxide Transparent Thin-Film Transistors Based on Amorphous Zinc Tin Oxide Fabricated at Room Temperature: Approaching the Thermodynamic Limit of the Subthreshold Swing. <i>Advanced Electronic Materials</i> , <b>2020</b> , 6, 2000423	6.4	6
676	A Most General and Facile Recipe for the Calculation of Heteroepitaxial Strain. <i>Physica Status Solidi (B): Basic Research</i> , <b>2020</b> , 257, 2000323	1.3	7
675	The principal axes systems for the elastic properties of monoclinic gallia. <i>Scientific Reports</i> , <b>2020</b> , 10, 19486	4.9	
674	Method of full polarization control of microwave fields in a scalable transparent structure for spin manipulation. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 194301	2.5	1
673	Low-Voltage Operation of Ring Oscillators Based on Room-Temperature-Deposited Amorphous Zinc-Tin-Oxide Channel MESFETs. <i>Advanced Electronic Materials</i> , <b>2019</b> , 5, 1900548	6.4	9
672	Band Offsets of Insulating & Semiconducting Oxides on (Al <sub>x</sub> Ga <sub>1-x</sub> )O <sub>3</sub> . <i>ECS Transactions</i> , <b>2019</b> , 92, 79-88	1	5
671	Heteroepitaxial growth of $\beta$ -Ga <sub>2</sub> O <sub>3</sub> phases by metalorganic vapor phase epitaxy. <i>Journal of Crystal Growth</i> , <b>2019</b> , 510, 76-84	1.6	38

670	Advances in designs and mechanisms of semiconducting metal oxide nanostructures for high-precision gas sensors operated at room temperature. <i>Materials Horizons</i> , <b>2019</b> , 6, 470-506	14.4	292
669	Polaronic interacceptor hopping transport in intrinsically doped nickel oxide. <i>Physical Review B</i> , <b>2019</b> , 99,	3.3	20
668	Modeling of a Waveguide-Based UV-VIS-IR Spectrometer Based on a Lateral (In,Ga)N Alloy Gradient. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1900170	1.6	2
667	Influence of Oxygen Pressure on Growth of Si-Doped $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ Thin Films on c-Sapphire Substrates by Pulsed Laser Deposition. <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, Q3217-Q3220 <sup>3</sup>		
666	High-Quality Schottky Barrier Diodes on Gallium Oxide Thin Films on Glass Substrate. <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, Q3126-Q3132	2	4
665	Electrical Properties of Vertical p-NiO/n-Ga <sub>2</sub> O <sub>3</sub> and p-ZnCo <sub>2</sub> O <sub>4</sub> /n-Ga <sub>2</sub> O <sub>3</sub> pn-Heterodiodes. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2019</b> , 216, 1800729	1.6	18
664	Coherent Polariton Modes and Lasing in ZnO Nano- and Microwires. <i>Physica Status Solidi (B): Basic Research</i> , <b>2019</b> , 256, 1800462	1.3	3
663	Valence band offsets for ALD SiO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> on $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.25-0.74$ . <i>APL Materials</i> , <b>2019</b> , 7, 071115	5.7	9
662	Band gap renormalization in n-type GeSn alloys made by ion implantation and flash lamp annealing. <i>Journal of Applied Physics</i> , <b>2019</b> , 125, 203105	2.5	6
661	Native Point Defect Measurement and Manipulation in ZnO Nanostructures. <i>Materials</i> , <b>2019</b> , 12,	3.5	12
660	Processing Strategies for High-Performance Schottky Contacts on n-Type Oxide Semiconductors: Insights from InO. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2019</b> , 11, 27073-27087	9.5	15
659	Full-Swing, High-Gain Inverters Based on ZnSnO JFETs and MESFETs. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 3376-3381	2.9	9
658	Band Alignment of Atomic Layer Deposited SiO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> on $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.2-0.65$ . <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, P351-P356	2	8
657	Record-Breaking Magnetoresistance at the Edge of a Microflake of Natural Graphite. <i>Advanced Engineering Materials</i> , <b>2019</b> , 21, 1900991	3.5	1
656	Applicability of the constitutive equations for the determination of the material properties of optically active materials. <i>Optics Letters</i> , <b>2019</b> , 44, 1351-1354	3	5
655	Structural, optical, and electrical properties of orthorhombic $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ thin films. <i>APL Materials</i> , <b>2019</b> , 7, 022525	5.7	24
654	Effect of Annealing on the Band Alignment of ALD SiO <sub>2</sub> on $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ for $x = 0.2 - 0.65$ . <i>ECS Journal of Solid State Science and Technology</i> , <b>2019</b> , 8, P751-P756	2	4
653	Femtosecond-time-resolved imaging of the dielectric function of ZnO in the visible to near-IR spectral range. <i>Applied Physics Letters</i> , <b>2019</b> , 115, 212103	3.4	8

652	Epitaxial stabilization of single phase $\text{In}_{1-x}\text{Ga}_x\text{O}_3$ thin films up to $x = 0.28$ on c-sapphire and $\text{Ga}_2\text{O}_3(001)$ templates by tin-assisted VCCS-PLD. <i>APL Materials</i> , <b>2019</b> , 7, 101102	5.7	24
651	Epitaxial $\text{Al}_x\text{Ga}_{1-x}\text{O}_3$ thin films and heterostructures grown by tin-assisted VCCS-PLD. <i>APL Materials</i> , <b>2019</b> , 7, 111110	5.7	17
650	Voigt Exceptional Points in an Anisotropic ZnO-Based Planar Microcavity: Square-Root Topology, Polarization Vortices, and Circularity. <i>Physical Review Letters</i> , <b>2019</b> , 123, 227401	7.4	16
649	Highly transparent conductors for optical and microwave access to spin-based quantum systems. <i>Npj Quantum Information</i> , <b>2019</b> , 5,	8.6	4
648	Tin-assisted heteroepitaxial PLD-growth of $\text{Ga}_2\text{O}_3$ thin films with high crystalline quality. <i>APL Materials</i> , <b>2019</b> , 7, 022516	5.7	63
647	Monolithic Waveguide-Based Linear Photodetector Array for Use as Ultracompact Spectrometer. <i>IEEE Transactions on Electron Devices</i> , <b>2019</b> , 66, 470-477	2.9	4
646	Record-Breaking Magnetoresistance at the Edge of a Microflake of Natural Graphite. <i>Advanced Engineering Materials</i> , <b>2019</b> , 21, 1970039	3.5	3
645	Impact of magnetization and hyperfine field distribution on high magnetoelectric coupling strength in $\text{BaTiO}_3\text{-BiFeO}_3$ multilayers. <i>Nanoscale</i> , <b>2018</b> , 10, 5574-5580	7.7	12
644	Properties of $\text{In}_2\text{S}_3$ -Based pin-Heterojunctions. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1700827	1.6	2
643	Effects of alloy composition and Si-doping on vacancy defect formation in $(\text{In}_x\text{Ga}_{1-x})\text{O}_3$ thin films. <i>Journal of Applied Physics</i> , <b>2018</b> , 123, 125705	2.5	6
642	Negative-U Properties of the Deep Level E3 in ZnO. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700670	1.3	3
641	Suppression of Grain Boundary Scattering in Multifunctional p-Type Transparent $\text{CuI}$ Thin Films due to Interface Tunneling Currents. <i>Advanced Materials Interfaces</i> , <b>2018</b> , 5, 1701411	4.6	16
640	Effect of double layer thickness on magnetoelectric coupling in multiferroic $\text{BaTiO}_3\text{-Bi}_{0.95}\text{Gd}_{0.05}\text{FeO}_3$ multilayers. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 184002	3	12
639	Defect Characterization, Imaging, and Control in Wide-Bandgap Semiconductors and Devices. <i>Journal of Electronic Materials</i> , <b>2018</b> , 47, 4980-4986	1.9	3
638	Evolution of magnetization in epitaxial $\text{Zn}_{1-x}\text{Fe}_x\text{O}$ thin films ( $0 \leq x \leq 0.66$ ) grown by pulsed laser deposition. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 245003	3	1
637	Optical signatures of deep level defects in $\text{Ga}_2\text{O}_3$ . <i>Applied Physics Letters</i> , <b>2018</b> , 112, 242102	3.4	82
636	Modeling of Schottky barrier diode characteristics on heteroepitaxial $\text{Ga}_{1-x}\text{Al}_x\text{O}_3$ thin films <b>2018</b> ,		4
635	Design of UV-crosslinked polymeric thin layers for encapsulation of piezoelectric ZnO nanowires for pressure-based fingerprint sensors. <i>Journal of Materials Chemistry C</i> , <b>2018</b> , 6, 605-613	7.1	12



634	Single Metal Ohmic and Rectifying Contacts to ZnO Nanowires: A Defect Based Approach. <i>Annalen Der Physik</i> , <b>2018</b> , 530, 1700335	2.6	10
633	Electrical conductivity of InO and GaO after low temperature ion irradiation; implications for intrinsic defect formation and charge neutrality level. <i>Journal of Physics Condensed Matter</i> , <b>2018</b> , 30, 025502	1.8	13
632	Temperature dependence of the dielectric function of thin film CuI in the spectral range (0.68.3) eV. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 172102	3.4	12
631	Elastic theory of pseudomorphic monoclinic and rhombohedral heterostructures. <i>Journal of Applied Physics</i> , <b>2018</b> , 124, 185302	2.5	20
630	Strain and Band-Gap Engineering in Ge-Sn Alloys via P Doping. <i>Physical Review Applied</i> , <b>2018</b> , 10,	4.3	10
629	Atomically stepped, pseudomorphic, corundum-phase (Al <sub>1-x</sub> Ga <sub>x</sub> ) <sub>2</sub> O <sub>3</sub> thin films (0.8x). <i>Applied Physics Letters</i> , <b>2018</b> , 113, 231902	3.4	14
628	Morphology-induced spin frustration in granular BiFeO <sub>3</sub> thin films: Origin of the magnetic vertical shift. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 142402	3.4	2
627	Tunable and switchable lasing in a ZnO microwire cavity at room temperature. <i>Journal Physics D: Applied Physics</i> , <b>2018</b> , 51, 425305	3	2
626	MESFETs and inverters based on amorphous zinc-tin-oxide thin films prepared at room temperature. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 133501	3.4	9
625	Monolithic Forward-Looking Photodetector for Use as Ultra-Compact Wavemeter with Wide Spectral Range. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2018</b> , 215, 1800651	1.6	
624	Defect Manipulation To Control ZnO Micro-/Nanowire-Metal Contacts. <i>Nano Letters</i> , <b>2018</b> , 18, 6974-6980	1.5	13
623	Photoinduced Heating of Graphitized Nanodiamonds Monitored by the Raman Diamond Peak. <i>Journal of Physical Chemistry C</i> , <b>2018</b> , 122, 25685-25691	3.8	3
622	Combinatorial Material Science and Strain Engineering Enabled by Pulsed Laser Deposition Using Radially Segmented Targets. <i>ACS Combinatorial Science</i> , <b>2018</b> , 20, 643-652	3.9	18
621	Spatiotemporal Evolution of Coherent Polariton Modes in ZnO Microwire Cavities at Room Temperature. <i>Nano Letters</i> , <b>2018</b> , 18, 6820-6825	11.5	13
620	Influence of Oxygen Deficiency on the Rectifying Behavior of Transparent-Semiconducting-Oxide/Metal Interfaces. <i>Physical Review Applied</i> , <b>2018</b> , 9,	4.3	23
619	Effect of annealing on the magnetic properties of zinc ferrite thin films. <i>Materials Letters</i> , <b>2017</b> , 195, 89-91	3.3	13
618	Exceptional points in anisotropic planar microcavities. <i>Physical Review A</i> , <b>2017</b> , 95,	2.6	12
617	Laser welding of fused silica glass with sapphire using a non- stoichiometric, fresnoitic Ba <sub>2</sub> TiSi <sub>2</sub> O <sub>8</sub> SiO <sub>2</sub> thin film as an absorber. <i>Optics and Laser Technology</i> , <b>2017</b> , 92, 85-94	4.2	6



616	Non-linear optical deformation potentials in uniaxially strained ZnO microwires. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 062103	3.4	2
615	Interface induced out-of-plane magnetic anisotropy in magnetoelectric BiFeO <sub>3</sub> -BaTiO <sub>3</sub> superlattices. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 092902	3.4	12
614	Low-Temperature PLD-Growth of Ultrathin ZnO Nanowires by Using Zn Al O and Zn Ga O Seed Layers. <i>Nanoscale Research Letters</i> , <b>2017</b> , 12, 134	5	7
613	Method of choice for the fabrication of high-quality gallium oxide-based Schottky diodes. <i>Semiconductor Science and Technology</i> , <b>2017</b> , 32, 065013	1.8	17
612	Strain in pseudomorphic monoclinic Ga <sub>2</sub> O <sub>3</sub> -based heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2017</b> , 254,	1.3	8
611	Copper iodide synthesized by iodization of Cu-films and deposited using MOCVD. <i>Journal of Crystal Growth</i> , <b>2017</b> , 471, 21-28	1.6	8
610	Schottky barrier diodes based on room temperature fabricated amorphous zinc tin oxide thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2017</b> , 214, 1700210	1.6	16
609	Investigation of the graphitization process of ion-beam irradiated diamond using ellipsometry, Raman spectroscopy and electrical transport measurements. <i>Carbon</i> , <b>2017</b> , 121, 512-517	10.4	13
608	Correlation of Interface Impurities and Chemical Gradients with High Magnetoelectric Coupling Strength in Multiferroic BiFeO <sub>3</sub> -BaTiO <sub>3</sub> Superlattices. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 18956-18965	9.5	16
607	Exceptional points in anisotropic photonic structures: from non-Hermitian physics to possible device applications <b>2017</b> ,		1
606	Charge transfer-induced magnetic exchange bias and electron localization in (111)- and (001)-oriented LaNiO <sub>3</sub> /LaMnO <sub>3</sub> superlattices. <i>Applied Physics Letters</i> , <b>2017</b> , 110, 102403	3.4	19
605	Dynamical Tuning of Nanowire Lasing Spectra. <i>Nano Letters</i> , <b>2017</b> , 17, 6637-6643	11.5	18
604	Ferromagnetic phase transition and single-gap type electrical conductivity of epitaxial LaMnO <sub>3</sub> /LaAlO <sub>3</sub> superlattices. <i>Journal Physics D: Applied Physics</i> , <b>2017</b> , 50, 43LT02	3	2
603	Temperature dependence of the dielectric tensor of monoclinic Ga <sub>2</sub> O <sub>3</sub> single crystals in the spectral range 1.08-5 eV. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 082102	3.4	13
602	Lasing in cuprous iodide microwires. <i>Applied Physics Letters</i> , <b>2017</b> , 111, 031105	3.4	11
601	Two-dimensional Frank-van-der-Merwe growth of functional oxide and nitride thin film superlattices by pulsed laser deposition. <i>Journal of Materials Research</i> , <b>2017</b> , 32, 3936-3946	2.5	7
600	Structure and cation distribution of (Mn <sub>0.5</sub> Zn <sub>0.5</sub> )Fe <sub>2</sub> O <sub>4</sub> thin films on SrTiO <sub>3</sub> (001). <i>Journal of Applied Physics</i> , <b>2017</b> , 121, 225305	2.5	1
599	Transparent flexible thermoelectric material based on non-toxic earth-abundant p-type copper iodide thin film. <i>Nature Communications</i> , <b>2017</b> , 8, 16076	17.4	164

598	Vital Role of Oxygen for the Formation of Highly Rectifying Schottky Barrier Diodes on Amorphous Zinc-Tin-Oxide with Various Cation Compositions. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2017</b> , 9, 26574-26581	9.5	17
597	Surface chemistry evolution of F-doped Ni-base superalloy upon heat treatment. <i>Materials and Corrosion - Werkstoffe Und Korrosion</i> , <b>2017</b> , 68, 220-227	1.6	1
596	Spatially-resolved cathodoluminescence spectroscopy of ZnO defects. <i>Materials Science in Semiconductor Processing</i> , <b>2017</b> , 57, 197-209	4.3	15
595	Optically anisotropic media: New approaches to the dielectric function, singular axes, microcavity modes and Raman scattering intensities. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2017</b> , 11, 1600295	2.5	14
594	Optical properties of epitaxial Na <sub>0.5</sub> Bi <sub>0.5</sub> TiO <sub>3</sub> lead-free piezoelectric thin films: Ellipsometric and theoretical studies. <i>Applied Surface Science</i> , <b>2017</b> , 421, 367-372	6.7	8
593	Program FFlexCom [High frequency flexible bendable electronics for wireless communication systems <b>2017</b> ,		6
592	Magnetic activity of surface plasmon resonance using dielectric magnetic materials fabricated on quartz glass substrate. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 07MC05	1.4	1
591	Induced ferromagnetism and magnetoelectric coupling in ion-beam synthesized BiFeO <sub>3</sub> /Fe <sub>2</sub> O <sub>4</sub> nanocomposite thin films. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 325302	3	15
590	Contacting ZnO Individual Crystal Facets by Direct Write Lithography. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 23891-8	9.5	2
589	Coexistence of strong and weak coupling in ZnO nanowire cavities. <i>EPJ Applied Physics</i> , <b>2016</b> , 74, 30502	1.1	2
588	Singular optical axes in biaxial crystals and analysis of their spectral dispersion effects in Ba <sub>2</sub> BO <sub>3</sub> . <i>Physical Review A</i> , <b>2016</b> , 93,	2.6	13
587	Cavity polariton condensate in a disordered environment. <i>Physical Review B</i> , <b>2016</b> , 93,	3.3	7
586	Raman Tensor Formalism for Optically Anisotropic Crystals. <i>Physical Review Letters</i> , <b>2016</b> , 116, 127401	7.4	45
585	Room-temperature Domain-epitaxy of Copper Iodide Thin Films for Transparent CuI/ZnO Heterojunctions with High Rectification Ratios Larger than 10 <sup>9</sup> . <i>Scientific Reports</i> , <b>2016</b> , 6, 21937	4.9	69
584	Raman tensor elements of EGaO. <i>Scientific Reports</i> , <b>2016</b> , 6, 35964	4.9	105
583	Room-temperature synthesized copper iodide thin film as degenerate p-type transparent conductor with a boosted figure of merit. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , <b>2016</b> , 113, 12929-12933	11.5	126
582	Wavelength-selective ultraviolet (Mg,Zn)O photodiodes: Tuning of parallel composition gradients with oxygen pressure. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 243503	3.4	6
581	Comparative study of optical and magneto-optical properties of normal, disordered, and inverse spinel-type oxides. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 429-436	1.3	18

580	Evaluation of the bond quality of laser-joined sapphire wafers using a fresnoite-glass sealant. <i>Microsystem Technologies</i> , <b>2016</b> , 22, 207-214	1.7	8
579	Influence of the Cation Ratio on Optical and Electrical Properties of Amorphous Zinc-Tin-Oxide Thin Films Grown by Pulsed Laser Deposition. <i>ACS Combinatorial Science</i> , <b>2016</b> , 18, 188-94	3.9	14
578	Semi-transparent NiO/ZnO UV photovoltaic cells. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 30-37	1.6	52
577	Laser-welded fused silica substrates using a luminescent fresnoite-based sealant. <i>Optics and Laser Technology</i> , <b>2016</b> , 80, 176-185	4.2	10
576	Defect segregation and optical emission in ZnO nano- and microwires. <i>Nanoscale</i> , <b>2016</b> , 8, 7631-7	7.7	44
575	The Physics of Semiconductors. <i>Graduate Texts in Physics</i> , <b>2016</b> ,	0.3	106
574	Correlation of High Magnetoelectric Coupling with Oxygen Vacancy Superstructure in Epitaxial Multiferroic BaTiO <sub>3</sub> /BiFeO <sub>3</sub> Composite Thin Films. <i>Materials</i> , <b>2016</b> , 9,	3.5	14
573	Electron transport mechanism in rf-sputtered amorphous zinc oxynitride thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 1767-1773	1.6	2
572	Carrier density driven lasing dynamics in ZnO nanowires. <i>Nanotechnology</i> , <b>2016</b> , 27, 225702	3.4	20
571	Pseudomorphic ZnO-based heterostructures: From polar through all semipolar to nonpolar orientations. <i>Physica Status Solidi (B): Basic Research</i> , <b>2016</b> , 253, 351-360	1.3	20
570	Ring Oscillators Based on ZnO Channel JFETs and MESFETs. <i>Advanced Electronic Materials</i> , <b>2016</b> , 2, 1500631	4.1	4
569	Epitaxial Coherence at Interfaces as Origin of High Magnetoelectric Coupling in Multiferroic BaTiO <sub>3</sub> /BiFeO <sub>3</sub> Superlattices. <i>Advanced Materials Interfaces</i> , <b>2016</b> , 3, 1500822	4.6	25
568	Confinement-driven metal-insulator transition and polarity-controlled conductivity of epitaxial LaNiO <sub>3</sub> /LaAlO <sub>3</sub> (111) superlattices. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 082108	3.4	11
567	Homoepitaxial nonpolar (10-10) ZnO/ZnMgO monolithic microcavities: Towards reduced photonic disorder. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 251904	3.4	12
566	Absorptive lasing mode suppression in ZnO nano- and microcavities. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 061102	3.4	10
565	Photo-enhanced magnetization in Fe-doped ZnO nanowires. <i>Applied Physics Letters</i> , <b>2016</b> , 109, 012401	3.4	4
564	Visible-blind and solar-blind ultraviolet photodiodes based on (In <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> . <i>Applied Physics Letters</i> , <b>2016</b> , 108, 123503	3.4	33
563	Growth Kinetics of Ultrathin ZnO Nanowires Grown by Pulsed Laser Deposition. <i>Procedia Engineering</i> , <b>2016</b> , 168, 1156-1159		2

562	Selective growth of tilted ZnO nanoneedles and nanowires by PLD on patterned sapphire substrates. <i>AIP Advances</i> , <b>2016</b> , 6, 095013	1.5	2
561	Realization of minimum number of rotational domains in heteroepitaxial Si(110) on 3C-SiC(001). <i>Applied Physics Letters</i> , <b>2016</b> , 108, 011608	3.4	4
560	Ellipsometric investigation of ZnFe <sub>2</sub> O <sub>4</sub> thin films in relation to magnetic properties. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 131901	3.4	12
559	Strong out-of-plane magnetic anisotropy in ion irradiated anatase TiO <sub>2</sub> thin films. <i>AIP Advances</i> , <b>2016</b> , 6, 125009	1.5	10
558	Temperature dependent self-compensation in Al- and Ga-doped Mg <sub>0.05</sub> Zn <sub>0.95</sub> O thin films grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 205703	2.5	3
557	Semitransparent ZnO-based UV-active solar cells: Analysis of electrical loss mechanisms. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2016</b> , 34, 04J107	1.3	10
556	Fundamental absorption edges in heteroepitaxial YBiO <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2016</b> , 120, 125702	2.5	1
555	Laser soldering of sapphire substrates using a BaTiAl <sub>6</sub> O <sub>12</sub> thin-film glass sealant. <i>Optics and Laser Technology</i> , <b>2016</b> , 81, 153-161	4.2	7
554	Oxide bipolar electronics: materials, devices and circuits. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 213001	3	67
553	Dipole analysis of the dielectric function of color dispersive materials: Application to monoclinic Ga <sub>2</sub> O <sub>3</sub> . <i>Physical Review B</i> , <b>2016</b> , 94,	3.3	44
552	The 2016 oxide electronic materials and oxide interfaces roadmap. <i>Journal Physics D: Applied Physics</i> , <b>2016</b> , 49, 433001	3	204
551	Semi-transparent NiO/ZnO UV photovoltaic cells (Phys. Status Solidi A 10016). <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2016</b> , 213, 224-224	1.6	3
550	Impact of sodium on the device characteristics of low temperature-deposited Cu(In,Ga)Se <sub>2</sub> -solar cells. <i>Thin Solid Films</i> , <b>2015</b> , 582, 85-90	2.2	10
549	Magnetic spin structure and magnetoelectric coupling in BiFeO <sub>3</sub> -BaTiO <sub>3</sub> multilayer. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 082904	3.4	22
548	Lethal suicidal attempt with a mixed-drug intoxication involving metoprolol and propafenone in first paediatric case report. <i>Clinical Therapeutics</i> , <b>2015</b> , 37, e7-e8	3.5	2
547	Fenofibrate-induced Anemia and Neutropenia in case report. <i>Clinical Therapeutics</i> , <b>2015</b> , 37, e103	3.5	3
546	Ion beam sputter deposition of Ge films: Influence of process parameters on film properties. <i>Thin Solid Films</i> , <b>2015</b> , 589, 487-492	2.2	22
545	Modeling the conductivity around the dimensionality-controlled metal-insulator transition in LaNiO <sub>3</sub> /LaAlO <sub>3</sub> (100) superlattices. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 042103	3.4	11

544	pn-Heterojunction Diodes with n-Type In <sub>2</sub> O <sub>3</sub> . <i>Advanced Electronic Materials</i> , <b>2015</b> , 1, 1400026	6.4	23
543	An aberration-corrected STEM study of structural defects in epitaxial GaN thin films grown by ion beam assisted MBE. <i>Micron</i> , <b>2015</b> , 73, 1-8	2.3	15
542	Study of the negative magneto-resistance of single proton-implanted lithium-doped ZnO microwires. <i>Journal of Physics Condensed Matter</i> , <b>2015</b> , 27, 256002	1.8	8
541	Transparent JFETs Based on $\text{p}^+\text{-NiO}/\text{n}^+\text{-ZnO}$ Heterojunctions. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 3999-4003	2.9	18
540	Electronic excitations and structure of Li <sub>2</sub> IrO <sub>3</sub> thin films grown on ZrO <sub>2</sub> :Y (001) substrates. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 025304	2.5	8
539	Low frequency noise of ZnO based metal-semiconductor field-effect transistors. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 033502	3.4	6
538	Lattice parameters and Raman-active phonon modes of $\text{E}(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ . <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 125703	2.5	59
537	Dielectric function in the spectral range (0.58.5)eV of an $(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ thin film with continuous composition spread. <i>Journal of Applied Physics</i> , <b>2015</b> , 117, 165307	2.5	37
536	Aluminium- and gallium-doped homoepitaxial ZnO thin films: Strain-engineering and electrical performance. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 1440-1447	1.6	3
535	Epitaxial stabilization of pseudomorphic $\text{E}\text{Ga}_2\text{O}_3$ on sapphire (0001). <i>Applied Physics Express</i> , <b>2015</b> , 8, 011101	2.4	82
534	Redshift of large wave vector LO phonon modes in wurtzite semiconductors due to the presence of free charge carriers. <i>Journal of Raman Spectroscopy</i> , <b>2015</b> , 46, 167-170	2.3	4
533	Comparison of Schottky contacts on $\text{E}\text{gallium}$ oxide thin films and bulk crystals. <i>Applied Physics Express</i> , <b>2015</b> , 8, 121102	2.4	40
532	Dielectric tensor of monoclinic Ga <sub>2</sub> O <sub>3</sub> single crystals in the spectral range 0.58.5 eV. <i>APL Materials</i> , <b>2015</b> , 3, 106106	5.7	65
531	Maxwell consideration of polaritonic quasi-particle Hamiltonians in multi-level systems. <i>Applied Physics Letters</i> , <b>2015</b> , 107, 231104	3.4	18
530	Electronic defects in In <sub>2</sub> O <sub>3</sub> and In <sub>2</sub> O <sub>3</sub> :Mg thin films on r-plane sapphire. <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 2304-2308	1.3	6
529	Eclipse Pulsed Laser Deposition for Damage-Free Preparation of Transparent ZnO Electrodes on Top of Organic Solar Cells. <i>Advanced Functional Materials</i> , <b>2015</b> , 25, 4321-4327	15.6	11
528	Karl B��ker (1877��1914) and the discovery of transparent conductive materials. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 1409-1426	1.6	14
527	LaNiO <sub>3</sub> films with tunable out-of-plane lattice parameter and their strain-related electrical properties. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 1925-1930	1.6	4

526	Karl Böker (1877-1914) and the discovery of transparent conductive materials. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 1407-1407	1.6	1
525	Doping efficiency and limits in (Mg,Zn)O:Al,Ga thin films with two-dimensional lateral composition spread. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 2850-2855	1.6	13
524	Theory of semiconductor solid and hollow nano- and microwires with hexagonal cross-section under torsion. <i>Physica Status Solidi (B): Basic Research</i> , <b>2015</b> , 252, 773-785	1.3	
523	Long-throw magnetron sputtering of amorphous ZnSnO thin films at room temperature. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2015</b> , 212, 1482-1486	1.6	14
522	All-Oxide Inverters Based on ZnO Channel JFETs With Amorphous ZnCo <sub>2</sub> O <sub>4</sub> Gates. <i>IEEE Transactions on Electron Devices</i> , <b>2015</b> , 62, 4004-4008	2.9	14
521	Local zincblende coordination in heteroepitaxial wurtzite Zn <sub>1-x</sub> Mg <sub>x</sub> O:Mn thin films with 0.01 <math>x</math> 0.04 identified by electron paramagnetic resonance. <i>Journal of Materials Chemistry C</i> , <b>2015</b> , 3, 11918-11929	2.1	2
520	Properties of Schottky Barrier Diodes on (In(x)Ga(1-x)) <sub>2</sub> O <sub>3</sub> For 0.01 <math>x</math> 0.85 Determined by a Combinatorial Approach. <i>ACS Combinatorial Science</i> , <b>2015</b> , 17, 710-5	3.9	23
519	Correlation of magnetoelectric coupling in multiferroic BaTiO <sub>3</sub> -BiFeO <sub>3</sub> superlattices with oxygen vacancies and antiphase octahedral rotations. <i>Applied Physics Letters</i> , <b>2015</b> , 106, 012905	3.4	49
518	Structural and optical properties of (In,Ga) <sub>2</sub> O <sub>3</sub> thin films and characteristics of Schottky contacts thereon. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 024005	1.8	47
517	From high-T <sub>c</sub> superconductors to highly correlated Mott insulators25 years of pulsed laser deposition of functional oxides in Leipzig. <i>Semiconductor Science and Technology</i> , <b>2015</b> , 30, 024003	1.8	3
516	All Amorphous Oxide Bipolar Heterojunction Diodes from Abundant Metals. <i>Advanced Electronic Materials</i> , <b>2015</b> , 1, 1400023	6.4	41
515	Parametric relaxation in whispering gallery mode exciton-polariton condensates. <i>Physical Review B</i> , <b>2015</b> , 91,	3.3	10
514	Laser welding of sapphire wafers using a thin-film fresnoite glass solder. <i>Microsystem Technologies</i> , <b>2015</b> , 21, 1035-1045	1.7	11
513	Ultrafast dynamics of the dielectric functions of ZnO and BaTiO <sub>3</sub> thin films after intense femtosecond laser excitation. <i>Journal of Applied Physics</i> , <b>2014</b> , 115, 053508	2.5	13
512	Raman active phonon modes of cubic In <sub>2</sub> O <sub>3</sub> . <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2014</b> , 8, 554-559	3.5	60
511	Breakdown characteristics of flexible Cu(In,Ga)Se <sub>2</sub> solar cells. <i>Solar Energy Materials and Solar Cells</i> , <b>2014</b> , 120, 506-511	6.4	17
510	Multiferroic BaTiO <sub>3</sub> /BiFeO <sub>3</sub> composite thin films and multilayers: strain engineering and magnetoelectric coupling. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 135303	3	83
509	Schottky contacts to In <sub>2</sub> O <sub>3</sub> . <i>APL Materials</i> , <b>2014</b> , 2, 046104	5.7	48



508	Electronic transitions and dielectric function tensor of a YMnO <sub>3</sub> single crystal in the NIR-VUV spectral range. <i>RSC Advances</i> , <b>2014</b> , 4, 33549-33554	3.7	11
507	Conducting behavior of chalcopyrite-type CuGaS <sub>2</sub> crystals under visible light. <i>Physical Chemistry Chemical Physics</i> , <b>2014</b> , 16, 21860-6	3.6	6
506	Local lattice distortions in oxygen deficient Mn-doped ZnO thin films, probed by electron paramagnetic resonance. <i>Journal of Materials Chemistry C</i> , <b>2014</b> , 2, 4947	7.1	26
505	Inhibition and enhancement of the spontaneous emission of quantum dots in micropillar cavities with radial-distributed Bragg reflectors. <i>ACS Nano</i> , <b>2014</b> , 8, 9970-8	16.7	23
504	( <sup>55</sup> Mn) pulsed ENDOR spectroscopy of Mn(2+) ions in ZnO thin films and single crystal. <i>Journal of Magnetic Resonance</i> , <b>2014</b> , 245, 79-86	3	6
503	Monolithic Multichannel Ultraviolet Photodiodes Based on (Mg,Zn)O Thin Films With Continuous Composition Spreads. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2014</b> , 20, 106-111	3.8	31
502	Highly textured fresnoite thin films synthesized in situ by pulsed laser deposition with CO <sub>2</sub> laser direct heating. <i>Journal Physics D: Applied Physics</i> , <b>2014</b> , 47, 034013	3	11
501	Improving the Optical Properties of Self-Catalyzed GaN Microrods toward Whispering Gallery Mode Lasing. <i>ACS Photonics</i> , <b>2014</b> , 1, 990-997	6.3	36
500	Interface recombination current in type II heterostructure bipolar diodes. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2014</b> , 6, 14785-9	9.5	45
499	Highly rectifying p-ZnCo <sub>2</sub> O <sub>4</sub> /n-ZnO heterojunction diodes. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 022104	3.4	40
498	Low rate deep level transient spectroscopy - a powerful tool for defect characterization in wide bandgap semiconductors. <i>Solid-State Electronics</i> , <b>2014</b> , 92, 40-46	1.7	8
497	30. The role of vitamin D for conception, polycystic ovary syndrome, endometriosis and the menstrual cycle. <i>Human Health Handbooks</i> , <b>2014</b> , 489-504		1
496	Layer-by-layer growth of TiN by pulsed laser deposition on in-situ annealed (100) MgO substrates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 2621-2624	1.6	14
495	Phonon-assisted lasing in ZnO microwires at room temperature. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 211106	3.4	8
494	Determination of the spontaneous polarization of wurtzite (Mg,Zn)O. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 192102	3.4	11
493	Dielectric function in the NIR-VUV spectral range of (In <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> thin films. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 053510	2.5	24
492	Impact of strain on electronic defects in (Mg,Zn)O thin films. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 103703	3.5	2
491	Temperature dependence of the dielectric function in the spectral range (0.58.5) eV of an In <sub>2</sub> O <sub>3</sub> thin film. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 111906	3.4	9



490	Control of the conductivity of Si-doped Ga <sub>2</sub> O <sub>3</sub> thin films via growth temperature and pressure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 34-39	1.6	79
489	X-ray multiple diffraction of ZnO substrates and heteroepitaxial thin films. <i>Physica Status Solidi (B): Basic Research</i> , <b>2014</b> , 251, 850-863	1.3	6
488	Defect studies on Ar-implanted ZnO thin films. <i>Physica Status Solidi (B): Basic Research</i> , <b>2014</b> , 251, 937-941	1.3	1
487	Determination of the mean and the homogeneous barrier height of Cu Schottky contacts on heteroepitaxial Ga <sub>2</sub> O <sub>3</sub> thin films grown by pulsed laser deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 40-47	1.6	95
486	Interface charging effects in ferroelectric ZnO/BaTiO <sub>3</sub> field-effect transistor heterostructures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2014</b> , 211, 166-172	1.6	6
485	Lattice parameters and Raman-active phonon modes of (In <sub>x</sub> Ga <sub>1-x</sub> ) <sub>2</sub> O <sub>3</sub> for x. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 013505	2.5	45
484	Modeling the electrical transport in epitaxial undoped and Ni-, Cr-, and W-doped TiO <sub>2</sub> anatase thin films. <i>Applied Physics Letters</i> , <b>2014</b> , 105, 062103	3.4	16
483	A continuous composition spread approach towards monolithic, wavelength-selective multichannel UV-photo-detector arrays. <i>Materials Research Society Symposia Proceedings</i> , <b>2014</b> , 1633, 123-129		6
482	Amorphous zinc-tin oxide thin films fabricated by pulsed laser deposition at room temperature. <i>Materials Research Society Symposia Proceedings</i> , <b>2014</b> , 1633, 101-104		14
481	A DLTS study of a ZnO microwire, a thin film and bulk material. <i>Materials Research Society Symposia Proceedings</i> , <b>2014</b> , 1633, 51-54		
480	Pulsed-Laser Deposition of ZnO Nanowires <b>2014</b> , 303-323		1
479	Several Approaches to Bipolar Oxide Diodes with High Rectification. <i>Advances in Science and Technology</i> , <b>2014</b> , 93, 252-259	0.1	10
478	Method of choice for fabrication of high-quality ZnO-based Schottky diodes. <i>Journal of Applied Physics</i> , <b>2014</b> , 116, 194506	2.5	29
477	An extended Drude model for the in-situ spectroscopic ellipsometry analysis of ZnO thin layers and surface modifications. <i>Thin Solid Films</i> , <b>2014</b> , 571, 437-441	2.2	8
476	Comparative study of deep defects in ZnO microwires, thin films and bulk single crystals. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 062102	3.4	9
475	One decade of fully transparent oxide thin-film transistors: fabrication, performance and stability. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2013</b> , 7, 605-615	2.5	28
474	Cuprous iodide as p-type transparent semiconductor: history and novel applications. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210, 1671-1703	1.6	111
473	Effect of sodium on material and device quality in low temperature deposited Cu(In,Ga)Se <sub>2</sub> . <i>Solar Energy Materials and Solar Cells</i> , <b>2013</b> , 119, 281-286	6.4	30

472	Degenerate interface layers in epitaxial scandium-doped ZnO thin films. <i>Journal Physics D: Applied Physics</i> , <b>2013</b> , 46, 065311	3	14
471	Determination of unscreened exciton states in polar ZnO/(Mg,Zn)O quantum wells with strong quantum-confined Stark effect. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	5
470	Vacuum ultraviolet dielectric function of ZnFe <sub>2</sub> O <sub>4</sub> thin films. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 073503	3.5	14
469	Surface- and point-defect-related Raman scattering in wurtzite semiconductors excited above the band gap. <i>New Journal of Physics</i> , <b>2013</b> , 15, 113048	2.9	20
468	Continuous composition spread using pulsed-laser deposition with a single segmented target. <i>CrystEngComm</i> , <b>2013</b> , 15, 10020	3.3	49
467	Effect of rare-earth ion doping on the multiferroic properties of BiFeO <sub>3</sub> thin films grown epitaxially on SrTiO <sub>3</sub> (1 0 0). <i>Journal Physics D: Applied Physics</i> , <b>2013</b> , 46, 175006	3	45
466	Growth control of nonpolar and polar quantum wells by pulsed-laser deposition. <i>Journal of Crystal Growth</i> , <b>2013</b> , 364, 81-87	1.6	9
465	Magnetic anisotropy of epitaxial zinc ferrite thin films grown by pulsed laser deposition. <i>Thin Solid Films</i> , <b>2013</b> , 527, 273-277	2.2	12
464	Transparent p-CuI/n-ZnO heterojunction diodes. <i>Applied Physics Letters</i> , <b>2013</b> , 102, 092109	3.4	114
463	Comparison of ZnO-Based JFET, MESFET, and MISFET. <i>IEEE Transactions on Electron Devices</i> , <b>2013</b> , 60, 1828-1833	2.9	21
462	Excitonic and Optical Confinement in Microwire Heterostructures with Nonpolar (Zn,Cd)O/(Mg,Zn)O Multiple Quantum Wells. <i>Journal of Physical Chemistry C</i> , <b>2013</b> , 117, 9020-9024	3.8	5
461	On the transition point of thermally activated conduction of spinel-type MFe <sub>2</sub> O <sub>4</sub> ferrite thin films (M = Zn, Co, Ni). <i>Applied Physics Letters</i> , <b>2013</b> , 102, 172104	3.4	23
460	Comparative study of transparent rectifying contacts on semiconducting oxide single crystals and amorphous thin films. <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 044511	2.5	21
459	Damp Heat Treatment of Cu(In,Ga)Se <sub>2</sub> Solar Cells with Different Sodium Content. <i>Materials</i> , <b>2013</b> , 6, 5478-5489	3.5	8
458	Energy-selective multichannel ultraviolet photodiodes based on (Mg,Zn)O. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 171111	3.4	27
457	Defect-induced magnetism in homoepitaxial manganese-stabilized zirconia thin films. <i>Journal Physics D: Applied Physics</i> , <b>2013</b> , 46, 275002	3	15
456	Temperature dependent dielectric function in the near-infrared to vacuum-ultraviolet ultraviolet spectral range of alumina and yttria stabilized zirconia thin films. <i>Journal of Applied Physics</i> , <b>2013</b> , 114, 223509	2.5	2
455	Tunneling dynamics of excitons in random semiconductor alloys. <i>Physical Review B</i> , <b>2013</b> , 87,	3.3	4

454	Mott variable-range hopping and weak antilocalization effect in heteroepitaxial Na <sub>2</sub> IrO <sub>3</sub> thin films. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	39
453	Martensitic phase transition and subsequent surface corrugation in manganese stabilized zirconia thin films. <i>Philosophical Magazine</i> , <b>2013</b> , 93, 2329-2339	1.6	
452	Cuprous iodide as p-type transparent semiconductor: history and novel applications (Phys. Status Solidi A 9013). <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2013</b> , 210,	1.6	86
451	Cytochrome P450 2D6 phenotype and genotype in hypertensive patients on long-term therapy with metoprolol. <i>Bratislava Medical Journal</i> , <b>2013</b> , 114, 206-12	1.7	1
450	ZnO-Based n-Channel Junction Field-Effect Transistor With Room-Temperature-Fabricated Amorphous p-Type $\text{ZnCo}_2\text{O}_4$ Gate. <i>IEEE Electron Device Letters</i> , <b>2012</b> , 33, 676-678	4.4	26
449	Microscopic Identification of Hot Spots in Multibarrier Schottky Contacts on Pulsed Laser Deposition Grown Zinc Oxide Thin Films. <i>IEEE Transactions on Electron Devices</i> , <b>2012</b> , 59, 536-541	2.9	6
448	(Zn,Cd)O thin films for the application in heterostructures: Structural and optical properties. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 103517	2.5	16
447	Exchange bias and magnetodielectric coupling effects in ZnFe <sub>2</sub> O <sub>4</sub> /BaTiO <sub>3</sub> composite thin films. <i>CrystEngComm</i> , <b>2012</b> , 14, 6477	3.3	25
446	Microwire (Mg,Zn)O/ZnO and (Mg,Zn)O/(Cd,Zn)O non-polar quantum well heterostructures for cavity applications. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 031110	3.4	12
445	On the investigation of electronic defect states in ZnO thin films by space charge spectroscopy with optical excitation. <i>Solid-State Electronics</i> , <b>2012</b> , 75, 48-54	1.7	9
444	The corner effect in hexagonal whispering gallery microresonators. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 141116	3.4	16
443	Persistent layer-by-layer growth for pulsed-laser homoepitaxy of $\bar{1}11$ ZnO. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2012</b> , 6, 433-435	2.5	7
442	Electronic and optical properties of ZnO/(Mg,Zn)O quantum wells with and without a distinct quantum-confined Stark effect. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 063701	2.5	21
441	Ballistic propagation of exciton-polariton condensates in a ZnO-based microcavity. <i>New Journal of Physics</i> , <b>2012</b> , 14, 013037	2.9	46
440	Exciton localization and phonon sidebands in polar ZnO/MgZnO quantum wells. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	11
439	Visible emission from ZnCdO/ZnO multiple quantum wells. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2012</b> , 6, 31-33	2.5	17
438	Whispering gallery modes in deformed hexagonal resonators. <i>Physica Status Solidi (B): Basic Research</i> , <b>2012</b> , 249, 871-879	1.3	26
437	Electrical transport in strained Mg <sub>x</sub> Zn <sub>1-x</sub> O:P thin films grown by pulsed laser deposition on ZnO(000-1). <i>Physica Status Solidi (B): Basic Research</i> , <b>2012</b> , 249, 82-90	1.3	4

436	On the T2 trap in zinc oxide thin films. <i>Physica Status Solidi (B): Basic Research</i> , <b>2012</b> , 249, 588-595	1.3	10
435	Oxidation state of tungsten oxide thin films used as gate dielectric for zinc oxide based transistors. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1494, 111-114		
434	Design rules of (Mg,Zn)O-based thin-film transistors with high- $\kappa$ WO <sub>3</sub> dielectric gates. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 183502	3.4	6
433	Optical and defect properties of hydrothermal ZnO with low lithium contamination. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 062105	3.4	16
432	On the radiation hardness of (Mg,Zn)O thin films grown by pulsed-laser deposition. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 012103	3.4	12
431	Modal gain and its diameter dependence in single-ZnO micro- and nanowires. <i>Semiconductor Science and Technology</i> , <b>2012</b> , 27, 015005	1.8	6
430	Excitonic transport in ZnO. <i>Journal of Materials Research</i> , <b>2012</b> , 27, 2225-2231	2.5	20
429	The (Mg,Zn)O Alloy <b>2012</b> , 257-319		9
428	Gate- and drain-lag effects in (Mg,Zn)O-based metal-semiconductor field-effect transistors. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 074515	2.5	3
427	Electrical transport and optical emission of Mn <sub>x</sub> Zr <sub>1-x</sub> O <sub>2</sub> (0.0-0.5) thin films. <i>Journal of Applied Physics</i> , <b>2011</b> , 110, 043706	2.5	6
426	MgZnO/ZnO quantum well nanowire heterostructures with large confinement energies. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>2011</b> , 29, 03A104	2.9	9
425	Ferrimagnetic ZnFe <sub>2</sub> O <sub>4</sub> thin films on SrTiO <sub>3</sub> single crystals with highly tunable electrical conductivity. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2011</b> , 5, 438-440	2.5	23
424	Transparent Rectifying Contacts for Visible-Blind Ultraviolet Photodiodes Based on ZnO. <i>Journal of Electronic Materials</i> , <b>2011</b> , 40, 473-476	1.9	8
423	Characterization of point defects in ZnO thin films by optical deep level transient spectroscopy. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 941-949	1.3	12
422	Formation of epitaxial domains: Unified theory and survey of experimental results. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 805-824	1.3	58
421	Nickel-related defects in ZnO [A deep-level transient spectroscopy and photo-capacitance study. <i>Physica Status Solidi (B): Basic Research</i> , <b>2011</b> , 248, 1949-1955	1.3	5
420	Tungsten oxide as a gate dielectric for highly transparent and temperature-stable zinc-oxide-based thin-film transistors. <i>Advanced Materials</i> , <b>2011</b> , 23, 5383-6	24	29
419	Fresnoite thin films grown by pulsed laser deposition: photoluminescence and laser crystallization. <i>CrystEngComm</i> , <b>2011</b> , 13, 6377	3.3	26

418	Defect properties of ZnO and ZnO:P microwires. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 013712	2.5	19
417	Semiconducting oxide heterostructures. <i>Semiconductor Science and Technology</i> , <b>2011</b> , 26, 014040	1.8	8
416	Thermal stability of ZnO/ZnCdO/ZnO double heterostructures grown by pulsed laser deposition. <i>Journal of Crystal Growth</i> , <b>2011</b> , 328, 13-17	1.6	7
415	Determination of the refractive index of single crystal bulk samples and micro-structures. <i>Thin Solid Films</i> , <b>2011</b> , 519, 2777-2781	2.2	18
414	Optical properties of BaTiO <sub>3</sub> /ZnO heterostructures under the effect of an applied bias. <i>Thin Solid Films</i> , <b>2011</b> , 519, 2933-2935	2.2	10
413	Exciton-polaritons in a ZnO-based microcavity: polarization dependence and nonlinear occupation. <i>New Journal of Physics</i> , <b>2011</b> , 13, 033014	2.9	9
412	Cavity-photon dispersion in one-dimensional confined microresonators with an optically anisotropic cavity material. <i>Physical Review B</i> , <b>2011</b> , 83,	3.3	13
411	Hafnium oxide thin films studied by time differential perturbed angular correlations. <i>Journal of Applied Physics</i> , <b>2011</b> , 109, 113918	2.5	1
410	Strain distribution in bent ZnO microwires. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 031105	3.4	41
409	Comment on Exciton-polariton microphotoluminescence and lasing from ZnO whispering-gallery mode microcavities[Appl. Phys. Lett. 98, 161110 (2011)]. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 136101	3.4	1
408	. <i>IEEE Electron Device Letters</i> , <b>2011</b> , 32, 515-517	4.4	3
407	Wavelength selective metal-semiconductor-metal photodetectors based on (Mg,Zn)O-heterostructures. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 083502	3.4	29
406	One- and two-dimensional cavity modes in ZnO microwires. <i>New Journal of Physics</i> , <b>2011</b> , 13, 103021	2.9	29
405	Population structure and historical biogeography of European <i>Arabidopsis lyrata</i> . <i>Heredity</i> , <b>2010</b> , 105, 543-53	3.6	19
404	Oxide Thin Film Heterostructures on Large Area, with Flexible Doping, Low Dislocation Density, and Abrupt Interfaces: Grown by Pulsed Laser Deposition. <i>Laser Chemistry</i> , <b>2010</b> , 2010, 1-27		21
403	Interface effects in ZnO metal-insulator-semiconductor and metal-semiconductor structures <b>2010</b> ,		1
402	Electrical Control of Magnetoresistance in Highly Insulating Co-Doped ZnO. <i>Japanese Journal of Applied Physics</i> , <b>2010</b> , 49, 043002	1.4	3
401	Ferromagnetic resonance on metal nanocrystals in Fe and Ni implanted ZnO. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 09B518	2.5	6

400	Identification of pre-breakdown mechanism of silicon solar cells at low reverse voltages. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 073506	3-4	37
399	Control of interface abruptness of polar MgZnO/ZnO quantum wells grown by pulsed laser deposition. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 052101	3-4	32
398	High-gain integrated inverters based on ZnO metal-semiconductor field-effect transistor technology. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 113502	3-4	21
397	Ultrathin gate-contacts for metal-semiconductor field-effect transistor devices: An alternative approach in transparent electronics. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 114515	2-5	15
396	Low-temperature processed Schottky-gated field-effect transistors based on amorphous gallium-indium-zinc-oxide thin films. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 243506	3-4	47
395	Identification of a donor-related recombination channel in ZnO thin films. <i>Physical Review B</i> , <b>2010</b> , 81,	3-3	14
394	Interface polarization coupling in piezoelectric-semiconductor ferroelectric heterostructures. <i>Physical Review B</i> , <b>2010</b> , 81,	3-3	35
393	Gold nanostructure matrices by diffraction mask-projection laser ablation: extension to previously inaccessible substrates. <i>Nanotechnology</i> , <b>2010</b> , 21, 175304	3-4	8
392	Competing exciton localization effects due to disorder and shallow defects in semiconductor alloys. <i>New Journal of Physics</i> , <b>2010</b> , 12, 033030	2-9	11
391	Electricity-to-Light Conversion. <i>Graduate Texts in Physics</i> , <b>2010</b> , 653-711	0-3	
390	Nanostructures. <i>Graduate Texts in Physics</i> , <b>2010</b> , 397-423	0-3	2
389	Crystals. <i>Graduate Texts in Physics</i> , <b>2010</b> , 35-71	0-3	
388	Defects. <i>Graduate Texts in Physics</i> , <b>2010</b> , 73-102	0-3	
387	Diodes. <i>Graduate Texts in Physics</i> , <b>2010</b> , 519-598	0-3	1
386	Defect-induced ferromagnetism in undoped and Mn-doped zirconia thin films. <i>Physical Review B</i> , <b>2010</b> , 82,	3-3	57
385	Luminescence properties of ZnO/Zn <sub>1-x</sub> Cd <sub>x</sub> O/ZnO double heterostructures. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 093530	2-5	14
384	The Physics of Semiconductors. <i>Graduate Texts in Physics</i> , <b>2010</b> ,	0-3	148
383	Origin of the near-band-edge luminescence in Mg <sub>x</sub> Zn <sub>1-x</sub> O alloys. <i>Journal of Applied Physics</i> , <b>2010</b> , 107, 013704	2-5	21



382	Tuning the lateral density of ZnO nanowire arrays and its application as physical templates for radial nanowire heterostructures. <i>Journal of Materials Chemistry</i> , <b>2010</b> , 20, 3848		23
381	Occurrence of rotation domains in heteroepitaxy. <i>Physical Review Letters</i> , <b>2010</b> , 105, 146102	7.4	62
380	Charge carrier dynamics of ZnO and ZnO-BaTiO <sub>3</sub> thin films. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 210, 012048	0.3	2
379	Ag related defect state in ZnO thin films <b>2010</b> ,		4
378	PLD Growth of High Reflective All-Oxide Bragg Reflectors for ZnO Resonators <b>2010</b> ,		3
377	Resistivity control of ZnO nanowires by Al doping. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2010</b> , 4, 82-84	2.5	14
376	Two-dimensional electron gases in MgZnO/ZnO heterostructures <b>2010</b> ,		1
375	The E3 Defect in Mg <sub>1-x</sub> Zn <sub>x</sub> O. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 584-588	1.9	6
374	Dielectric Passivation of ZnO-Based Schottky Diodes. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 559-562	1.9	12
373	Shallow Donors and Compensation in Homoepitaxial ZnO Thin Films. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 595-600	1.9	5
372	Identification of a Deep Acceptor Level in ZnO Due to Silver Doping. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 577-583	1.9	15
371	Recent progress on ZnO-based metal-semiconductor field-effect transistors and their application in transparent integrated circuits. <i>Advanced Materials</i> , <b>2010</b> , 22, 5332-49	24	122
370	Mikroskopischer Mechanismus der spezifischen Adhäsion von Peptiden an Halbleitersubstraten. <i>Angewandte Chemie</i> , <b>2010</b> , 122, 9721-9724	3.6	
369	Microscopic mechanism of specific peptide adhesion to semiconductor substrates. <i>Angewandte Chemie - International Edition</i> , <b>2010</b> , 49, 9530-3	16.4	44
368	Morphological, structural and electrical investigations on non-polar a-plane ZnO epilayers. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 2078-2082	1.6	33
367	Optical properties of homo- and heteroepitaxial ZnO/Mg <sub>x</sub> Zn <sub>1-x</sub> O single quantum wells grown by pulsed-laser deposition. <i>Journal of Luminescence</i> , <b>2010</b> , 130, 520-526	3.8	30
366	Homoepitaxial Mg <sub>x</sub> Zn <sub>1-x</sub> O (0.00-0.22) thin films grown by pulsed laser deposition. <i>Thin Solid Films</i> , <b>2010</b> , 518, 4623-4629	2.2	8
365	Observation of strong light-matter coupling by spectroscopic ellipsometry. <i>Superlattices and Microstructures</i> , <b>2010</b> , 47, 19-23	2.8	8



364	Donor-Acceptor pair recombination in non-stoichiometric ZnO thin films. <i>Solid State Communications</i> , <b>2010</b> , 150, 379-382	1.6	3
363	Transparent semiconducting oxides: materials and devices. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 1437-1449	1.6	120
362	Structural characterization of H plasma-doped ZnO single crystals by Hall measurements and photoluminescence studies. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2010</b> , 207, 2426-2431	1.6	2
361	Electronic coupling in ZnO/MgxZn1-xO double quantum wells grown by pulsed-laser deposition. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 398-404	1.3	8
360	Self-organized growth of ZnO-based nano- and microstructures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1265-1281	1.3	38
359	Architecture of nano- and microdimensional building blocks. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1257-1264	1.3	5
358	Whispering gallery modes in zinc oxide micro- and nanowires. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1282-1293	1.3	66
357	Two-dimensional confined photonic wire resonators & strong light-matter coupling. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1351-1364	1.3	15
356	Defects in a nitrogen-implanted ZnO thin film. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1220-1236	1.3	17
355	Tubular magnetic nanostructures based on glancing angle deposited templates and atomic layer deposition. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1365-1371	1.3	21
354	Synthesis and physical properties of cylindrite micro tubes and lamellae. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1335-1350	1.3	5
353	Voigt effect measurement on PLD grown NiO thin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 334-337		3
352	Magnetic Semiconductors. <i>Graduate Texts in Physics</i> , <b>2010</b> , 441-449	0.3	4
351	Band Structure. <i>Graduate Texts in Physics</i> , <b>2010</b> , 139-183	0.3	1
350	Dielectric Structures. <i>Graduate Texts in Physics</i> , <b>2010</b> , 481-509	0.3	
349	Recombination. <i>Graduate Texts in Physics</i> , <b>2010</b> , 309-344	0.3	
348	Transistors. <i>Graduate Texts in Physics</i> , <b>2010</b> , 713-766	0.3	
347	Heterostructures. <i>Graduate Texts in Physics</i> , <b>2010</b> , 347-378	0.3	

346	Polarized Semiconductors. <i>Graduate Texts in Physics</i> , <b>2010</b> , 425-439	0.3	
345	Resistive hysteresis and interface charge coupling in BaTiO <sub>3</sub> -ZnO heterostructures. <i>Applied Physics Letters</i> , <b>2009</b> , 94, 142904	3-4	49
344	ZnO-based metal-semiconductor field-effect transistors on glass substrates. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 153503	3-4	14
343	Bound-exciton recombination in Mg <sub>x</sub> Zn <sub>1-x</sub> O thin films. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1201, 78		
342	Lineshape theory of photoluminescence from semiconductor alloys. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 123521	2-5	33
341	Polarization behavior of the exciton-polariton emission of ZnO-based microresonators. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1208, 1		0
340	MgZnO:P homoepitaxy by pulsed laser deposition: pseudomorphic layer-by-layer growth and high electron mobility <b>2009</b> ,		8
339	Defects in zinc-implanted ZnO thin films. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1597		12
338	Temperature dependence of localization effects of excitons in ZnO <sub>1-x</sub> Zn <sub>1-x</sub> O <sub>x</sub> double heterostructures. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1741		16
337	Dopant activation in homoepitaxial MgZnO:P thin films. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1604		7
336	Strong exciton-photon coupling in ZnO based resonators. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1726		10
335	Optical characterization of zinc oxide microlasers and microwire core-shell heterostructures. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1780		6
334	Electrical properties of ZnO/BaTiO <sub>3</sub> /ZnO heterostructures with asymmetric interface charge distribution. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 082902	3-4	22
333	Electronic coupling in Mg <sub>x</sub> Zn <sub>1-x</sub> O/ZnO double quantum wells. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1735		6
332	Light beam induced current measurements on ZnO Schottky diodes and MESFETs. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1201, 84		2
331	ZnO nano-pillar resonators with coaxial Bragg reflectors. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1178, 13		1
330	ZnO-based MESFET Devices. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1201, 30		1
329	Temperature-Dependent Properties of Nearly Ideal ZnO Schottky Diodes. <i>IEEE Transactions on Electron Devices</i> , <b>2009</b> , 56, 2160-2164	2-9	33

328	Magnetic and structural properties of transition metal doped zinc-oxide nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2009</b> , 246, 766-770	1.3	10
327	Studies towards freestanding GaN in hydride vapor phase epitaxy by in-situ etching of a sacrificial ZnO buffer layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2009</b> , 6, S352-S355		10
326	ZnO-based metal-semiconductor field-effect transistors with Ag-, Pt-, Pd-, and Au-Schottky gates. <i>Thin Solid Films</i> , <b>2009</b> , 518, 1119-1123	2.2	18
325	Formation of a two-dimensional electron gas in ZnO/MgZnO single heterostructures and quantum wells. <i>Thin Solid Films</i> , <b>2009</b> , 518, 1048-1052	2.2	30
324	Ferromagnetic transition metal implanted ZnO: A diluted magnetic semiconductor?. <i>Vacuum</i> , <b>2009</b> , 83, S13-S19	3.7	38
323	Correlation of pre-breakdown sites and bulk defects in multicrystalline silicon solar cells. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2009</b> , 3, 70-72	2.5	57
322	Paramagnetism in Co-doped ZnO films. <i>Journal Physics D: Applied Physics</i> , <b>2009</b> , 42, 085001	3	36
321	Homogeneous core/shell ZnO/ZnMgO quantum well heterostructures on vertical ZnO nanowires. <i>Nanotechnology</i> , <b>2009</b> , 20, 305701	3.4	39
320	Defect-induced magnetic order in pure ZnO films. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	257
319	Anionic and cationic substitution in ZnO. <i>Progress in Solid State Chemistry</i> , <b>2009</b> , 37, 153-172	8	81
318	Observation of strong exciton-photon coupling at temperatures up to 410 K. <i>New Journal of Physics</i> , <b>2009</b> , 11, 073044	2.9	40
317	Properties of reactively sputtered Ag, Au, Pd, and Pt Schottky contacts on n-type ZnO. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1769		68
316	Ferroelectric thin film field-effect transistors based on ZnO/BaTiO <sub>3</sub> heterostructures. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1789		25
315	Stable p-type ZnO:P nanowire/n-type ZnO:Ga film junctions, reproducibly grown by two-step pulsed laser deposition. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 1693		17
314	Zinc oxide nanorod based photonic devices: recent progress in growth, light emitting diodes and lasers. <i>Nanotechnology</i> , <b>2009</b> , 20, 332001	3.4	503
313	Genetic discontinuity, breeding-system change and population history of <i>Arabis alpina</i> in the Italian Peninsula and adjacent Alps. <i>Molecular Ecology</i> , <b>2008</b> , 17, 2245-57	5.7	52
312	Room temperature ferromagnetism in ZnO films due to defects. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 082508	3.4	310
311	Intense white photoluminescence emission of V-implanted zinc oxide thin films. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 123504	2.5	24

310	Room temperature ferromagnetism in Nd- and Mn-codoped ZnO films. <i>Journal Physics D: Applied Physics</i> , <b>2008</b> , 41, 105012	3	23
309	Spatial fluctuations of optical emission from single ZnO/MgZnO nanowire quantum wells. <i>Nanotechnology</i> , <b>2008</b> , 19, 115202	3-4	36
308	Interface-charge-coupled polarization response model of Pt-BaTiO <sub>3</sub> -ZnO-Pt heterojunctions: Physical parameters variation. <i>Materials Research Society Symposia Proceedings</i> , <b>2008</b> , 1074, 1		
307	Room temperature ferromagnetism in carbon-implanted ZnO. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 232507	3-4	178
306	Whispering gallery mode lasing in zinc oxide microwires. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 241102	3-4	178
305	High electron mobility of phosphorous-doped homoepitaxial ZnO thin films grown by pulsed-laser deposition. <i>Journal of Applied Physics</i> , <b>2008</b> , 104, 013708	2-5	27
304	ZnO metal-semiconductor field-effect transistors with Ag-Schottky gates. <i>Applied Physics Letters</i> , <b>2008</b> , 92, 192108	3-4	62
303	Spin manipulation in Co-doped ZnO. <i>Physical Review Letters</i> , <b>2008</b> , 101, 076601	7-4	55
302	Surface modification of Co-doped ZnO nanocrystals and its effects on the magnetic properties. <i>Journal of Applied Physics</i> , <b>2008</b> , 103, 07D140	2-5	16
301	Phosphorous doped ZnO nanowires: acceptor-related cathodoluminescence and p-type conducting FET-characteristics <b>2008</b> ,		2
300	Electronic properties of shallow level defects in ZnO grown by pulsed laser deposition. <i>Journal of Physics: Conference Series</i> , <b>2008</b> , 100, 042038	0-3	4
299	Properties of homoepitaxial ZnO and ZnO:P thin films grown by pulsed-laser deposition <b>2008</b> ,		2
298	Exciton-Polariton formation at room temperature in a planar ZnO resonator structure. <i>Applied Physics B: Lasers and Optics</i> , <b>2008</b> , 93, 331-337	1-9	40
297	Interface-Charge-Coupled Polarization Response of Pt-BaTiO <sub>3</sub> -ZnO-Pt Heterojunctions: A Physical Model Approach. <i>Journal of Electronic Materials</i> , <b>2008</b> , 37, 1029-1034	1-9	19
296	Investigation of the free charge carrier properties at the ZnO-sapphire interface in a-plane ZnO films studied by generalized infrared ellipsometry. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1350-1353		2
295	Structural and optical properties of ZnO <sub>2</sub> and Al <sub>2</sub> O <sub>3</sub> thin films and Bragg reflectors grown by pulsed laser deposition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1240-1243		17
294	Electrooptic ellipsometry study of piezoelectric BaTiO <sub>3</sub> -ZnO heterostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 1328-1331		4
293	Homoepitaxial ZnO thin films by PLD: Structural properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 3280-3287		22

292	A practical, self-catalytic, atomic layer deposition of silicon dioxide. <i>Angewandte Chemie - International Edition</i> , <b>2008</b> , 47, 6177-9	16.4	120
291	MOVPE growth of GaN around ZnO nanopillars. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5139-5142	1.6	11
290	Exciton-phonon coupling and exciton thermalization in Mg <sub>x</sub> Zn <sub>1-x</sub> O thin films. <i>Solid State Communications</i> , <b>2008</b> , 148, 570-572	1.6	14
289	Magnetotransport properties of Zn <sub>90</sub> Mn <sub>7.5</sub> Cu <sub>2.5</sub> O <sub>100</sub> films. <i>Thin Solid Films</i> , <b>2008</b> , 516, 1160-1163	2.2	9
288	Magnetic and transport properties of Cu <sub>1.05</sub> Cr <sub>0.89</sub> Mg <sub>0.05</sub> O <sub>2</sub> and Cu <sub>0.96</sub> Cr <sub>0.95</sub> Mg <sub>0.05</sub> Mn <sub>0.04</sub> O <sub>2</sub> films. <i>Thin Solid Films</i> , <b>2008</b> , 516, 8543-8546	2.2	
287	Growth and Characterization of ZnO Nano- and Microstructures <b>2008</b> , 293-323		2
286	p-type conducting ZnO:P microwires prepared by direct carbothermal growth. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2008</b> , 2, 37-39	2.5	44
285	ZnO nanowall networks grown on DiMPLA pre-patterned thin gold films. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2008</b> , 2, 200-202	2.5	9
284	Structure and optical properties of ZnO nanowires fabricated by pulsed laser deposition on GaN/Si(111) films with the use of Au and NiO catalysts. <i>Bulletin of the Russian Academy of Sciences: Physics</i> , <b>2008</b> , 72, 1129-1131	0.4	
283	Dependence of Trap Concentrations in ZnO Thin Films on Annealing Conditions. <i>Journal of the Korean Physical Society</i> , <b>2008</b> , 53, 2861-2863	0.6	16
282	Vacuum Ultraviolet Dielectric Function and Band Structure of ZnO. <i>Journal of the Korean Physical Society</i> , <b>2008</b> , 53, 88-93	0.6	7
281	Growth Evolution and Characterization of PLD Zn(Mg)O Nanowire Arrays <b>2008</b> , 113-125		3
280	Photocurrent spectroscopy of deep levels in ZnO thin films. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	27
279	Optical Properties of Cyndrite. <i>AIP Conference Proceedings</i> , <b>2007</b> ,	0	3
278	Photoluminescence of Mg <sub>x</sub> Zn <sub>1-x</sub> O/ZnO Quantum Wells Grown by Pulsed Laser Deposition. <i>AIP Conference Proceedings</i> , <b>2007</b> ,	0	3
277	Temperature dependence of the whispering gallery effect in ZnO nanoresonators. <i>AIP Conference Proceedings</i> , <b>2007</b> ,	0	2
276	ZnO based planar and micropillar resonators. <i>Superlattices and Microstructures</i> , <b>2007</b> , 41, 360-363	2.8	15
275	A zinc oxide microwire laser. <i>Superlattices and Microstructures</i> , <b>2007</b> , 41, 347-351	2.8	15

274	Comparative characterization of differently grown ZnO single crystals by positron annihilation and Hall effect. <i>Superlattices and Microstructures</i> , <b>2007</b> , 42, 259-264	2.8	17
273	Investigation of acceptor states in ZnO by junction DLTS. <i>Superlattices and Microstructures</i> , <b>2007</b> , 42, 14-20	2.8	4
272	Electrical and magnetic properties of RE-doped ZnO thin films (RE = Gd, Nd). <i>Superlattices and Microstructures</i> , <b>2007</b> , 42, 231-235	2.8	67
271	Optical whispering gallery modes in dodecagonal zinc oxide microcrystals. <i>Superlattices and Microstructures</i> , <b>2007</b> , 42, 333-336	2.8	22
270	Electronic properties of defects in pulsed-laser deposition grown ZnO with levels at 300 and 370meV below the conduction band. <i>Physica B: Condensed Matter</i> , <b>2007</b> , 401-402, 378-381	2.8	27
269	InGaN/GaN nanopillar-array light emitting diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2007</b> , 4, 1605-1608		7
268	Defects in N <sup>+</sup> ion-implanted ZnO single crystals studied by positron annihilation and Hall effect. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2007</b> , 4, 3642-3645		2
267	MOCVD regrowth of InGaN on N-polar and Ga-polar pillar and stripe nanostructures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2007</b> , 244, 1802-1805	1.3	3
266	Recombination diversifies chloroplast trnF pseudogenes in Arabidopsis lyrata. <i>Journal of Evolutionary Biology</i> , <b>2007</b> , 20, 2400-11	2.3	30
265	Homoepitaxy of ZnO by pulsed-laser deposition. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2007</b> , 1, 129-131	2.5	38
264	Cathodoluminescence of large-area PLD grown ZnO thin films measured in transmission and reflection. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 88, 89-93	2.6	5
263	Optical and structural properties of MgZnO/ZnO hetero- and double heterostructures grown by pulsed laser deposition. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 88, 99-104	2.6	28
262	Properties of phosphorus doped ZnO. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 88, 125-128		24
261	Donor-like defects in ZnO substrate materials and ZnO thin films. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 88, 135-139	2.6	47
260	Pulsed-laser deposition and characterization of ZnO nanowires with regular lateral arrangement. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 88, 31-34	2.6	30
259	Electrical and optical spectroscopy on ZnO:Co thin films. <i>Applied Physics A: Materials Science and Processing</i> , <b>2007</b> , 88, 157-160	2.6	6
258	Exact solutions for the capacitance of space charge regions at semiconductor interfaces. <i>Solid-State Electronics</i> , <b>2007</b> , 51, 1002-1004	1.7	7
257	A comparison between ZnO films doped with 3d and 4f magnetic ions. <i>Thin Solid Films</i> , <b>2007</b> , 515, 8761-8763		33



256	Phosphorus acceptor doped ZnO nanowires prepared by pulsed-laser deposition. <i>Nanotechnology</i> , <b>2007</b> , 18, 455707	3.4	96
255	Polarization coupling in epitaxial ZnO / BaTiO <sub>3</sub> thin film heterostructures on SrTiO <sub>3</sub> (100) substrates <b>2007</b> , 6474, 290		5
254	Ordered growth of tilted ZnO nanowires: morphological, structural and optical characterization. <i>Nanotechnology</i> , <b>2007</b> , 18, 195303	3.4	42
253	Magnetoresistance and anomalous Hall effect in magnetic ZnO films. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 063918	2.5	39
252	Meyer-Neldel rule in ZnO. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 232110	3.4	10
251	Luminescence and surface properties of Mg <sub>x</sub> Zn <sub>1-x</sub> O thin films grown by pulsed laser deposition. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 083521	2.5	47
250	Co location and valence state determination in ferromagnetic ZnO:Co thin films by atom-location-by-channeling-enhanced-microanalysis electron energy-loss spectroscopy. <i>Applied Physics Letters</i> , <b>2007</b> , 90, 154101	3.4	15
249	$\sigma$ exchange interaction induced magnetoresistance in magnetic ZnO. <i>Physical Review B</i> , <b>2007</b> , 76,	3.3	61
248	Defects in hydrothermally grown bulk ZnO. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 022913	3.4	49
247	Demonstration of an ultraviolet ZnO-based optically pumped third order distributed feedback laser. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 111108	3.4	17
246	Room temperature ferromagnetism in Mn-doped ZnO films mediated by acceptor defects. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 092503	3.4	80
245	Temperature-dependence of the refractive index and the optical transitions at the fundamental band-gap of ZnO. <i>AIP Conference Proceedings</i> , <b>2007</b> ,	0	13
244	Valence Band Structure of ZnO and Mg <sub>x</sub> Zn <sub>1-x</sub> O. <i>Materials Research Society Symposia Proceedings</i> , <b>2007</b> , 1035, 1		
243	Electron paramagnetic resonance in transition metal-doped ZnO nanowires. <i>Journal of Applied Physics</i> , <b>2007</b> , 101, 024324	2.5	29
242	Weak ferromagnetism in textured Zn <sub>1-x</sub> (TM) <sub>x</sub> O thin films. <i>Superlattices and Microstructures</i> , <b>2006</b> , 39, 334-339	2.8	14
241	Growth and Characterization of Optical and Electrical Properties of ZnO Nano- and Microwires. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 957, 1		1
240	Interface and Luminescence Properties of Pulsed Laser Deposited Mg <sub>x</sub> Zn <sub>1-x</sub> O/ZnO Quantum Wells with Strong Confinement. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 957, 1		5
239	Phonon modes, dielectric constants, and exciton mass parameters in ternary Mg <sub>x</sub> Zn <sub>1-x</sub> O. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 928, 1		1



- 238 Spin polarization in Zn<sub>0.95</sub>Co<sub>0.05</sub>O:(Al,Cu) thin films. *Journal Physics D: Applied Physics*, **2006**, 39, 4920-4924 11
- 237 Temperature Dependent Hall Measurements on PLD Thin Films. *Materials Research Society Symposia Proceedings*, **2006**, 957, 1 9
- 236 Defects in virgin and N<sup>+</sup>-implanted ZnO single crystals studied by positron annihilation, Hall effect, and deep-level transient spectroscopy. *Physical Review B*, **2006**, 74, 3-3 129
- 235 Thermally assisted tunneling processes in In<sub>x</sub>Ga<sub>1-x</sub>As/GaAs quantum-dot structures. *Physical Review B*, **2006**, 74, 3-3 12
- 234 Deep acceptor states in ZnO single crystals. *Applied Physics Letters*, **2006**, 89, 092122 3-4 63
- 233 Mean barrier height of Pd Schottky contacts on ZnO thin films. *Applied Physics Letters*, **2006**, 88, 092102 3-4 146
- 232 Refractive indices and band-gap properties of rocksalt Mg<sub>x</sub>Zn<sub>1-x</sub>O (0.68 ≤ x ≤ 1). *Journal of Applied Physics*, **2006**, 99, 123701 2-5 51
- 231 Magnetoresistance effects in Zn<sub>0.90</sub>Co<sub>0.10</sub>O films. *Journal of Applied Physics*, **2006**, 100, 013904 2-5 26
- 230 Metal-insulator transition in Co-doped ZnO: Magnetotransport properties. *Physical Review B*, **2006**, 73, 3-3 77
- 229 Pseudopotential band structures of rocksalt MgO, ZnO, and Mg<sub>1-x</sub>Zn<sub>x</sub>O. *Applied Physics Letters*, **2006**, 88, 134104 3-4 52
- 228 Infrared optical properties of Mg<sub>x</sub>Zn<sub>1-x</sub>O thin films (0 ≤ x ≤ 1): Long-wavelength optical phonons and dielectric constants. *Journal of Applied Physics*, **2006**, 99, 113504 2-5 72
- 227 Structural characterization of a-plane Zn<sub>1-x</sub>Cd<sub>x</sub>O (0 ≤ x ≤ 0.085) thin films grown by metal-organic vapor phase epitaxy. *Journal of Applied Physics*, **2006**, 99, 023514 2-5 59
- 226 Fast, high-efficiency, and homogeneous room-temperature cathodoluminescence of ZnO scintillator thin films on sapphire. *Applied Physics Letters*, **2006**, 89, 243510 3-4 27
- 225 Cluster properties of peptides on (100) semiconductor surfaces. *Langmuir*, **2006**, 22, 8104-8 4 18
- 224 Quantitative scanning capacitance microscopy. *Physica B: Condensed Matter*, **2006**, 376-377, 913-915 2.8 2
- 223 Ferromagnetic behavior in Zn(Mn, P)O thin films. *Physics Letters, Section A: General, Atomic and Solid State Physics*, **2006**, 351, 323-326 2-3 6
- 222 Room-temperature ferromagnetic Mn-alloyed ZnO films obtained by pulsed laser deposition. *Journal of Magnetism and Magnetic Materials*, **2006**, 307, 212-221 2.8 38
- 221 Structure and ferromagnetism of Mn<sup>+</sup> ion-implanted ZnO thin films on sapphire. *Superlattices and Microstructures*, **2006**, 39, 41-49 2.8 13

220	Deep defects generated in n-conducting ZnO:TM thin films. <i>Solid State Communications</i> , <b>2006</b> , 137, 417-421	2.2	14
219	Low temperature photoluminescence and infrared dielectric functions of pulsed laser deposited ZnO thin films on silicon. <i>Thin Solid Films</i> , <b>2006</b> , 496, 234-239	2.2	20
218	Magnetoresistance in pulsed laser deposited 3d transition metal doped ZnO films. <i>Thin Solid Films</i> , <b>2006</b> , 515, 2549-2554	2.2	18
217	Growth and characterization of Mn- and Co-doped ZnO nanowires. <i>Mikrochimica Acta</i> , <b>2006</b> , 156, 21-25	5.8	13
216	MgxZn1-xO (0 ≤ x ≤ 1). <i>Applied Physics Letters</i> , <b>2005</b> , 86, 1431-13	3.4	181
215	Rectifying semiconductor-ferroelectric polarization loops and offsets in PtBaTiO3/nO/Pt thin film capacitor structures. <i>Thin Solid Films</i> , <b>2005</b> , 486, 153-157	2.2	31
214	Two-dimensional ZnO:Al nanosheets and nanowalls obtained by Al2O3-assisted carbothermal evaporation. <i>Thin Solid Films</i> , <b>2005</b> , 486, 191-194	2.2	34
213	EPR study on magnetic Zn1-xMnxO. <i>Superlattices and Microstructures</i> , <b>2005</b> , 38, 413-420	2.8	23
212	Electrical properties of ZnO thin films and optical properties of ZnO-based nanostructures. <i>Superlattices and Microstructures</i> , <b>2005</b> , 38, 317-328	2.8	25
211	The bias dependence of the non-radiative recombination current in p-n diodes. <i>Solid-State Electronics</i> , <b>2005</b> , 49, 1446-1448	1.7	5
210	Cylindric resonators with coaxial Bragg reflectors <b>2005</b> ,		3
209	UV optical properties of ferromagnetic Mn-doped ZnO thin films grown by PLD. <i>Thin Solid Films</i> , <b>2005</b> , 486, 117-121	2.2	65
208	Room-temperature cathodoluminescence of n-type ZnO thin films grown by pulsed laser deposition in N2, N2O, and O2 background gas. <i>Thin Solid Films</i> , <b>2005</b> , 486, 205-209	2.2	20
207	a-Si/SiOx Bragg-reflectors on micro-structured InP. <i>Thin Solid Films</i> , <b>2005</b> , 483, 257-260	2.2	3
206	Quantum Devices of Reduced Dimensionality <b>2005</b> , 17-22		1
205	Combined Raman scattering, X-ray fluorescence and ellipsometry in-situ growth monitoring of CuInSe2-based photoabsorber layers on polyimide substrates. <i>AIP Conference Proceedings</i> , <b>2005</b> ,	0	2
204	Incorporation and electrical activity of group V acceptors in ZnO thin films. <i>AIP Conference Proceedings</i> , <b>2005</b> ,	0	6
203	Band-to-band transitions and optical properties of MgxZn1-xO (0 ≤ x ≤ 1) films. <i>AIP Conference Proceedings</i> , <b>2005</b> ,	0	6

202	Optical Resonances Of Single Zinc Oxide Microcrystals. <i>AIP Conference Proceedings</i> , <b>2005</b> ,	0	2
201	Low-order optical whispering-gallery modes in hexagonal nanocavities. <i>Physical Review A</i> , <b>2005</b> , 72,	2.6	102
200	Electron paramagnetic resonance of Zn <sub>1-x</sub> MnxO thin films and single crystals. <i>Physical Review B</i> , <b>2005</b> , 72,	3.3	58
199	Donor Levels in ZnO. <i>Advances in Solid State Physics</i> , <b>2005</b> , 263-274		38
198	Temperature-dependent dielectric and electro-optic properties of a ZnO-BaTiO <sub>3</sub> -ZnO heterostructure grown by pulsed-laser deposition. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 091904	3.4	49
197	Electrical Properties of ZnO Thin Films and Single Crystals. <i>NATO Science Series Series II, Mathematics, Physics and Chemistry</i> , <b>2005</b> , 47-57		4
196	Whispering Gallery Modes in Hexagonal Zinc Oxide Micro- and Nanocrystals <b>2005</b> , 83-98		1
195	Infrared dielectric functions and crystal orientation of a-plane ZnO thin films on r-plane sapphire determined by generalized ellipsometry. <i>Thin Solid Films</i> , <b>2004</b> , 455-456, 161-166	2.2	31
194	UV-VIS spectroscopic ellipsometry of ternary Mg <sub>x</sub> Zn <sub>1-x</sub> O (0.53) thin films. <i>Thin Solid Films</i> , <b>2004</b> , 455-456, 500-504	2.2	38
193	Band dispersion relations of zinc-blende and wurtzite InN. <i>Physical Review B</i> , <b>2004</b> , 69,	3.3	74
192	Cathodoluminescence of selected single ZnO nanowires on sapphire. <i>Annalen Der Physik</i> , <b>2004</b> , 13, 39-42.	4.6	47
191	Pulsed laser deposition of Fe- and Fe, Cu-doped ZnO thin films. <i>Annalen Der Physik</i> , <b>2004</b> , 13, 57-58	2.6	4
190	Advances of pulsed laser deposition of ZnO thin films. <i>Annalen Der Physik</i> , <b>2004</b> , 13, 59-60	2.6	15
189	Electro-optical properties of ZnO-BaTiO <sub>3</sub> -ZnO heterostructures grown by pulsed laser deposition. <i>Annalen Der Physik</i> , <b>2004</b> , 13, 61-62	2.6	14
188	Spatially Inhomogeneous Impurity Distribution in ZnO Micropillars. <i>Nano Letters</i> , <b>2004</b> , 4, 797-800	11.5	74
187	Binding Specificity of a Peptide on Semiconductor Surfaces. <i>Nano Letters</i> , <b>2004</b> , 4, 2115-2120	11.5	105
186	Whispering gallery modes in nanosized dielectric resonators with hexagonal cross section. <i>Physical Review Letters</i> , <b>2004</b> , 93, 103903	7.4	270
185	Infrared dielectric function and phonon modes of Mg-rich cubic Mg <sub>x</sub> Zn <sub>1-x</sub> O (x=0.67) thin films on sapphire (0001). <i>Applied Physics Letters</i> , <b>2004</b> , 85, 905-907	3.4	29

184	Lateral homogeneity of Schottky contacts on n-type ZnO. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 79-81	3.4	95
183	Slow N-acetyltransferase 2 status leads to enhanced intrastriatal dopamine depletion in 6-hydroxydopamine-lesioned rats. <i>Experimental Neurology</i> , <b>2004</b> , 187, 199-202	5.7	8
182	COMPARISON OF THE EFFECT OF CORDIPIN RETARD AND CORDIPIN XL IN CHILDREN WITH HYPERTENSION. <i>Journal of Hypertension</i> , <b>2004</b> , 22, S256-S257	1.9	
181	Microwave properties of epitaxial large-area Ca-doped YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-<math>\delta</math></sub> thin films on r-plane sapphire. <i>Solid-State Electronics</i> , <b>2003</b> , 47, 2183-2186	1.7	11
180	Dielectric properties of Fe-doped Ba <sub>x</sub> Sr <sub>1-x</sub> TiO <sub>3</sub> thin films on polycrystalline substrates at temperatures between 35 and +85 °C. <i>Solid-State Electronics</i> , <b>2003</b> , 47, 2199-2203	1.7	20
179	Optical and electrical properties of epitaxial (Mg,Cd) <sub>x</sub> Zn <sub>1-x</sub> O, ZnO, and ZnO:(Ga,Al) thin films on c-plane sapphire grown by pulsed laser deposition. <i>Solid-State Electronics</i> , <b>2003</b> , 47, 2205-2209	1.7	130
178	Infrared dielectric functions and phonon modes of high-quality ZnO films. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 126-133	2.5	545
177	Nanoscroll formation from strained layer heterostructures. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 2444-2446	3.4	103
176	Band-structure pseudopotential calculation of zinc-blende and wurtzite AlN, GaN, and InN. <i>Physical Review B</i> , <b>2003</b> , 67,	3.3	108
175	Dielectric functions (1 to 5 eV) of wurtzite Mg <sub>x</sub> Zn <sub>1-x</sub> O (x $\geq$ 0.29) thin films. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 2260-2262	3.4	157
174	Raman scattering in ZnO thin films doped with Fe, Sb, Al, Ga, and Li. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1974-1976	3.4	551
173	High electron mobility of epitaxial ZnO thin films on c-plane sapphire grown by multistep pulsed-laser deposition. <i>Applied Physics Letters</i> , <b>2003</b> , 82, 3901-3903	3.4	539
172	High-quality reproducible PLD YBaCuO:Ag thin films up to 4 inch diameter for microwave applications. <i>Physica C: Superconductivity and Its Applications</i> , <b>2002</b> , 372-376, 587-589	1.3	9
171	Long-wavelength quantum-dot lasers. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2002</b> , 13, 643-647	2.1	4
170	Infrared dielectric functions and phonon modes of wurtzite Mg <sub>x</sub> Zn <sub>1-x</sub> O (x $\geq$ 0.2). <i>Applied Physics Letters</i> , <b>2002</b> , 81, 2376-2378	3.4	64
169	Comment on Problems in recent analysis of injected carrier dynamics in semiconductor quantum dots[Appl. Phys. Lett. 79, 3912 (2001)]. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 565-565	3.4	1
168	Nonequilibrium Spectroscopy of Inter- and Intraband Transitions in Quantum Dot Structures. <i>Materials Science Forum</i> , <b>2002</b> , 384-385, 39-42	0.4	
167	Injection Lasers Based on Intraband Carrier Transitions. <i>Materials Science Forum</i> , <b>2002</b> , 384-385, 209-212	0.4	

166	Far-infrared magneto-optical generalized ellipsometry determination of free-carrier parameters in semiconductor thin film structures. <i>Materials Research Society Symposia Proceedings</i> , <b>2002</b> , 744, 1		1
165	Copper genes are not implicated in the pathogenesis of focal dystonia. <i>Neurology</i> , <b>2002</b> , 59, 782-3	6.5	7
164	Theory of Quantum Dot Lasers. <i>Nanoscience and Technology</i> , <b>2002</b> , 299-316	0.6	3
163	Quantum dot lasers: Theory and experiment. <i>AIP Conference Proceedings</i> , <b>2001</b> ,	0	2
162	Influence of P-glycoprotein on the transplacental passage of cyclosporine. <i>Journal of Pharmaceutical Sciences</i> , <b>2001</b> , 90, 1583-92	3.9	60
161	Novel Infrared Quantum Dot Lasers: Theory and Reality. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 787-796	1.3	30
160	High Power Quantum Dot Lasers at 1160 nm. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 819-822	1.3	9
159	Large Modal Gain of InAs/GaAs Quantum Dot Lasers. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 823-826	1.3	5
158	Radiative Inter-Sublevel Transitions in InGaAs/AlGaAs Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 833-837	1.3	3
157	Stability of Biexcitons in Pyramidal InAs/GaAs Quantum Dots. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 115-118	1.3	30
156	Enhanced Radiation Hardness of InAs/GaAs Quantum Dot Structures. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 93-96	1.3	37
155	Exciton Level Crossing in Coupled InAs/GaAs Quantum Dot Pairs. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 224, 405-408	1.3	20
154	Maximum modal gain of a self-assembled InAs/GaAs quantum-dot laser. <i>Journal of Applied Physics</i> , <b>2001</b> , 90, 1666-1668	2.5	55
153	Optical phenomena connected with intraband carrier transitions in quantum dots and quantum wells. <i>Nanotechnology</i> , <b>2001</b> , 12, 462-465	3.4	3
152	Comment: Room-temperature long-wavelength (= 13.3 [micro sign]m) unipolar quantum dot intersubband laser. <i>Electronics Letters</i> , <b>2001</b> , 37, 96	1.1	2
151	Enhanced radiation hardness of quantum dot lasers to high energy proton irradiation. <i>Electronics Letters</i> , <b>2001</b> , 37, 174	1.1	56
150	Calorimetric investigation of intersublevel transitions in charged quantum dots. <i>Physical Review B</i> , <b>2001</b> , 64,	3.3	6
149	Close-to-ideal device characteristics of high-power InGaAs/GaAs quantum dot lasers. <i>Applied Physics Letters</i> , <b>2001</b> , 78, 1207-1209	3.4	184

148	Near- and mid-infrared spectroscopy of InGaAs/GaAs quantum dot structures. <i>Nanotechnology</i> , <b>2001</b> , 12, 447-449	3.4	1
147	. <i>IEEE Journal of Quantum Electronics</i> , <b>2001</b> , 37, 418-425	2	33
146	Effect of excited-state transitions on the threshold characteristics of a quantum dot laser <b>2000</b> ,		4
145	Atomic Structure Based Simulation of X-Ray Scattering from Strained Superlattices. <i>Physica Status Solidi (B): Basic Research</i> , <b>2000</b> , 218, 417-423	1.3	7
144	Optical Properties of Self-Organized Quantum Dots: Modeling and Experiments. <i>Physica Status Solidi A</i> , <b>2000</b> , 178, 255-262		31
143	Quantum Dot Structures in the InGaAs System Investigated by TEM Techniques. <i>Crystal Research and Technology</i> , <b>2000</b> , 35, 759-768	1.3	16
142	Surface flattening during MOCVD of thin GaAs layers covering InGaAs quantum dots. <i>Journal of Crystal Growth</i> , <b>2000</b> , 221, 581-585	1.6	29
141	Quantum dot lasers: breakthrough in optoelectronics. <i>Thin Solid Films</i> , <b>2000</b> , 367, 235-249	2.2	157
140	Carrier emission processes in InAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>2000</b> , 7, 388-392	3	5
139	Quantum-dot heterostructure lasers. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2000</b> , 6, 439-451	3.8	139
138	Quantum dots for GaAs-based surface emitting lasers at 1300 nm <b>2000</b> , 589-597		1
137	Progress in Quantum Dot Lasers: 1100 nm, 1300 nm, and High Power Applications. <i>Japanese Journal of Applied Physics</i> , <b>2000</b> , 39, 2341-2343	1.4	36
136	Relaxation oscillations of quantum dot lasers. <i>Electronics Letters</i> , <b>2000</b> , 36, 1851	1.1	3
135	Electronic structure of cleaved-edge-overgrowth strain-induced quantum wires. <i>Physical Review B</i> , <b>2000</b> , 61, 1744-1747	3.3	8
134	Feasibility of 5 Gbit/s wavelength division multiplexing using quantum dot lasers. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 4265-4267	3.4	16
133	Separation of strain and quantum-confinement effects in the optical spectra of quantum wires. <i>Physical Review B</i> , <b>2000</b> , 61, 4488-4491	3.3	13
132	Midinfrared emission from near-infrared quantum-dot lasers. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 4-6	3.4	47
131	Many-body effects on the optical spectra of InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>2000</b> , 62, 16881-16885	3.3	57

130	High-power quantum-dot lasers at 1100 nm. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 556-558	3.4	96
129	How a quantum-dot laser turns on. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 1428-1430	3.4	29
128	Diode lasers based on quantum dots <b>1999</b> , 203-214		2
127	The present status of quantum dot lasers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1999</b> , 5, 167-184	3	177
126	Hot carrier relaxation in InAs/GaAs quantum dots. <i>Physica B: Condensed Matter</i> , <b>1999</b> , 272, 8-11	2.8	14
125	Quantum dot lasers: recent progress in theoretical understanding and demonstration of high-output-power operation. <i>Applied Physics B: Lasers and Optics</i> , <b>1999</b> , 69, 413-416	1.9	22
124	Electronic and optical properties of strained quantum dots modeled by 8-band k <p> theory. <i>Physical Review B</i>, <b>1999</b>, 59, 5688-5701</p>	3.3	908
123	Electron escape from InAs quantum dots. <i>Physical Review B</i> , <b>1999</b> , 60, 14265-14268	3.3	138
122	An EXAFS study on thiolcapped CdTe nanocrystals. <i>Zeitschrift Fur Elektrotechnik Und Elektrochemie</i> , <b>1998</b> , 102, 1561-1564		15
121	Carrier statistics in quantum-dot lasers. <i>Physics of the Solid State</i> , <b>1998</b> , 40, 772-774	0.8	1
120	Influence of In/Ga intermixing on the optical properties of InGaAs/GaAs quantum dots. <i>Journal of Crystal Growth</i> , <b>1998</b> , 195, 540-545	1.6	62
119	Lateral association of vertically-coupled quantum dots. <i>Microelectronic Engineering</i> , <b>1998</b> , 43-44, 37-43	2.5	14
118	Formation of InSb quantum dots in a GaSb matrix using molecular-beam epitaxy. <i>Microelectronic Engineering</i> , <b>1998</b> , 43-44, 85-90	2.5	13
117	Formation of InSb quantum dots in a GaSb matrix. <i>Journal of Electronic Materials</i> , <b>1998</b> , 27, 414-417	1.9	12
116	Staggered grids hybrid-dual spectral element method for second-order elliptic problems application to high-order time splitting methods for Navier-Stokes equations. <i>Computer Methods in Applied Mechanics and Engineering</i> , <b>1998</b> , 166, 183-199	5.7	8
115	Semiconductor quantum dots for application in diode lasers. <i>Thin Solid Films</i> , <b>1998</b> , 318, 83-87	2.2	13
114	Edge and vertical cavity surface emitting InAs quantum dot lasers. <i>Solid-State Electronics</i> , <b>1998</b> , 42, 1433-1437	1.4	14
113	Hot carrier relaxation in InAs/GaAs quantum dots. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 578-582	3	21



112	New approach to modeling carrier distribution in quantum dot ensembles: Gain and threshold of QD lasers and impact of phonon bottleneck. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 2, 725-728	3	2
111	Application of self-organized quantum dots to edge emitting and vertical cavity lasers. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , <b>1998</b> , 3, 129-136	3	21
110	Effects of growth interruption on uniformity of GaAs quantum wires formed on vicinal GaAs(110) surfaces by MBE. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1998</b> , 51, 229-232	3.1	2
109	Optical properties of InAlAs quantum dots in an AlGaAs matrix. <i>Applied Surface Science</i> , <b>1998</b> , 123-124, 381-384	6.7	16
108	Correlation of InGaAs/GaAs quantum dot and wetting layer formation. <i>Applied Surface Science</i> , <b>1998</b> , 123-124, 352-355	6.7	11
107	Approximation of the Wave and Electromagnetic Diffusion Equations by Spectral Method. <i>SIAM Journal of Scientific Computing</i> , <b>1998</b> , 20, 13-32	2.6	13
106	The contribution of particle core and surface to strain, disorder and vibrations in thiolcapped CdTe nanocrystals. <i>Journal of Chemical Physics</i> , <b>1998</b> , 108, 7807-7815	3.9	143
105	Carrier dynamics in type-II GaSb/GaAs quantum dots. <i>Physical Review B</i> , <b>1998</b> , 57, 4635-4641	3.3	213
104	Growth, Spectroscopy, and Laser Application of Self-Ordered III-V Quantum Dots. <i>MRS Bulletin</i> , <b>1998</b> , 23, 31-34	3.2	90
103	Excited states and energy relaxation in stacked InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1998</b> , 57, 9050-9060	3.3	209
102	Formation of InAs quantum dots on a silicon (100) surface. <i>Semiconductor Science and Technology</i> , <b>1998</b> , 13, 1262-1265	1.8	46
101	Electronic states in strained cleaved-edge-overgrowth quantum wires and quantum dots. <i>Physical Review B</i> , <b>1998</b> , 58, 10557-10561	3.3	16
100	InAs/GaAs Quantum Dots Grown by Metalorganic Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4129-4133	1.4	20
99	Lateral and vertical ordering in multilayered self-organized InGaAs quantum dots studied by high resolution x-ray diffraction. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 955-957	3.4	76
98	High Resolution X-Ray Diffraction and Reflectivity Studies of Vertical and Lateral Ordering in Multiple Self-Organized InGaAs Quantum Dots. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4084-4087 <sup>1.4</sup>		4
97	Selbstordnende Quantenpunkte: Vom Festkörper zum Atom. <i>Physik Journal</i> , <b>1997</b> , 53, 517-522		10
96	Gain and Threshold of Quantum Dot Lasers: Theory and Comparison to Experiments. <i>Japanese Journal of Applied Physics</i> , <b>1997</b> , 36, 4181-4187	1.4	98
95	Theory of random population for quantum dots. <i>Physical Review B</i> , <b>1997</b> , 55, 9740-9745	3.3	272

94	Quantum wires in staggered-band-line-up single heterostructures with corrugated interfaces. <i>Physical Review B</i> , <b>1997</b> , 55, 7733-7742	3.3	7
93	Formation of quantum dots in twofold cleaved edge overgrowth. <i>Physical Review B</i> , <b>1997</b> , 55, 4054-4056	3.3	24
92	Three-dimensional arrays of self-ordered quantum dots for laser applications. <i>Microelectronics Journal</i> , <b>1997</b> , 28, 915-931	1.8	13
91	Structural characterization of self-assembled quantum dot structures by X-ray diffraction techniques. <i>Thin Solid Films</i> , <b>1997</b> , 306, 198-204	2.2	12
90	Luminescence properties of semiconductor quantum dots. <i>Journal of Luminescence</i> , <b>1997</b> , 72-74, 34-37	3.8	14
89	Carrier Dynamics in Quantum Dots: Modeling with Master Equations for the Transitions between Micro-States. <i>Physica Status Solidi (B): Basic Research</i> , <b>1997</b> , 203, 121-132	1.3	30
88	Theory of Quantum Dot Laser Gain and Threshold: Correlated versus Uncorrelated Electron and Hole Capture. <i>Physica Status Solidi A</i> , <b>1997</b> , 164, 297-300		16
87	Uniform GaAs quantum wires formed on vicinal GaAs (110) surfaces by two-step MBE growth. <i>Superlattices and Microstructures</i> , <b>1997</b> , 22, 43-49	2.8	16
86	Low pressure metal-organic chemical vapor deposition of InP/InAlAs/InGaAs quantum wires. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 590-594	1.6	6
85	Self organization phenomena of quantum dots grown by metalorganic chemical vapour deposition. <i>Journal of Crystal Growth</i> , <b>1997</b> , 170, 568-573	1.6	54
84	Self-Ordering of Nanostructures on Semiconductor Surfaces <b>1997</b> , 257-302		2
83	Asymptotic solution of natural convection problem in a square cavity heated from below. <i>International Journal of Numerical Methods for Heat and Fluid Flow</i> , <b>1996</b> , 6, 29-36	4.5	5
82	Nature of optical transitions in self-organized InAs/GaAs quantum dots. <i>Physical Review B</i> , <b>1996</b> , 53, R10509-R10511	3.3	105
81	Excited states in self-organized InAs/GaAs quantum dots: Theory and experiment. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 979-981	3.4	203
80	Zero-dimensional excitons in (Zn,Cd)Se quantum structures. <i>Physical Review B</i> , <b>1996</b> , 54, R11074-R11077	3.3	63
79	Direct formation of vertically coupled quantum dots in Stranski-Krastanow growth. <i>Physical Review B</i> , <b>1996</b> , 54, 8743-8750	3.3	452
78	Strain-induced formation and tuning of ordered nanostructures on crystal surfaces. <i>Surface Science</i> , <b>1996</b> , 352-354, 117-122	1.8	34
77	An intermediate (1.0-1.5 monolayers) stage of heteroepitaxial growth of InAs on GaAs(100) during submonolayer molecular beam epitaxy. <i>Surface Science</i> , <b>1996</b> , 352-354, 646-650	1.8	17

76	STM and RHEED study of quantum dots obtained by submonolayer epitaxial techniques. <i>Surface Science</i> , <b>1996</b> , 352-354, 651-655	1.8	24
75	Exciton relaxation in self-organized InAs/GaAs quantum dots. <i>Surface Science</i> , <b>1996</b> , 361-362, 770-773	1.8	6
74	Evolution of deep levels and internal photoemission with annealing temperature at ZnSe/GaAs interfaces. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1996</b> , 14, 2961		5
73	Self-organization processes of InGaAs/GaAs quantum dots grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 3284-3286	3.4	86
72	TEM Structural Characterization of NM-Scale Islands in Highly Mismatched Systems. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 421, 383		3
71	Electronic structure and energy relaxation in strained InAs/GaAs quantum pyramids. <i>Superlattices and Microstructures</i> , <b>1996</b> , 19, 81-95	2.8	45
70	Photo- and cathodoluminescence of AlGaAs single quantum wires on vicinal GaAs (110) surfaces. <i>Solid-State Electronics</i> , <b>1996</b> , 40, 319-322	1.7	6
69	Ordered arrays of quantum dots: Formation, electronic spectra, relaxation phenomena, lasing. <i>Solid-State Electronics</i> , <b>1996</b> , 40, 785-798	1.7	186
68	Size-dependent luminescence of GaAs quantum wires on vicinal GaAs (110) surfaces with giant steps formed by MBE. <i>Physica B: Condensed Matter</i> , <b>1996</b> , 227, 291-294	2.8	7
67	Diffusion induced disordering (DID) in superlattices. <i>Journal of Crystal Growth</i> , <b>1996</b> , 159, 514-517	1.6	6
66	InP/InAlAs/InGaAs quantum wires. <i>III-Vs Review</i> , <b>1996</b> , 9, 32-38		
65	InAs-GaAs quantum dots: From growth to lasers. <i>Physica Status Solidi (B): Basic Research</i> , <b>1996</b> , 194, 159-173	1.3	61
64	Multiphonon-relaxation processes in self-organized InAs/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 361-363	3.4	206
63	InGaAs quantum wires grown by low pressure metalorganic chemical vapor deposition on InP V-grooves. <i>Applied Physics Letters</i> , <b>1996</b> , 68, 3596-3598	3.4	40
62	InAs/GaAs Quantum Pyramid Lasers: In Situ Growth, Radiative Lifetimes and Polarization Properties. <i>Japanese Journal of Applied Physics</i> , <b>1996</b> , 35, 1311-1319	1.4	144
61	Pseudomorphic InAs/GaAs quantum dots on low index planes		10
60	InAs/GaAs quantum dots radiative recombination from zero-dimensional states. <i>Physica Status Solidi (B): Basic Research</i> , <b>1995</b> , 188, 249-258	1.3	119
59	Formation of AlGaAs quantum wires on vicinal GaAs(110) surfaces misoriented 3° toward (111)A by molecular beam epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1995</b> , 35, 295-298	3.1	3

58	High quantum efficiency InP mesas grown by hybrid epitaxy on Si substrates. <i>Journal of Crystal Growth</i> , <b>1995</b> , 156, 337-342	1.6	7
57	Optical spectroscopy of self-organized nanoscale hetero-structures involving high-index surfaces. <i>Microelectronics Journal</i> , <b>1995</b> , 26, 871-879	1.8	19
56	Self-organization processes in MBE-grown quantum dot structures. <i>Thin Solid Films</i> , <b>1995</b> , 267, 32-36	2.2	100
55	Maskless selective area growth of InP on Sub- $\mu$ m V-groove patterned Si(001). <i>Journal of Electronic Materials</i> , <b>1995</b> , 24, 1625-1629	1.9	1
54	Radiative recombination in type-II GaSb/GaAs quantum dots. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 656-658	3.4	284
53	Ordering phenomena in InAs strained layer morphological transformation on GaAs (100) surface. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 97-99	3.4	63
52	Electron quantum wires in type II single heterostructures on nonplanar substrates. <i>Applied Physics Letters</i> , <b>1995</b> , 67, 1712-1714	3.4	12
51	ELECTRONIC AND OPTICAL PROPERTIES OF QUASI-ONE-DIMENSIONAL CARRIERS IN QUANTUM WIRES. <i>Journal of Nonlinear Optical Physics and Materials</i> , <b>1995</b> , 04, 99-140	0.8	30
50	Chronische Elektrostimulation des Nucleus ventralis intermedius des Thalamus zur Tremorbehandlung. <i>Aktuelle Neurologie</i> , <b>1995</b> , 22, 176-180		9
49	Epitaxial liftoff InGaAs/InP MSM photodetectors on Si. <i>Electronics Letters</i> , <b>1995</b> , 31, 1383-1384	1.1	17
48	Structural characterization of (In,Ga)As quantum dots in a GaAs matrix. <i>Physical Review B</i> , <b>1995</b> , 51, 14766-14768	3.4	14768
47	Ultrasharp Luminescence Lines from Single Quantum Dots. <i>Physical Review Letters</i> , <b>1995</b> , 74, 4043-4046	3.4	645
46	InAs/GaAs pyramidal quantum dots: Strain distribution, optical phonons, and electronic structure. <i>Physical Review B</i> , <b>1995</b> , 52, 11969-11981	3.3	1062
45	Radiative states in type-II GaSb/GaAs quantum wells. <i>Physical Review B</i> , <b>1995</b> , 52, 14058-14066	3.3	192
44	High-speed InGaAs on Si metal-semiconductor-metal photodetectors. <i>Electronics Letters</i> , <b>1994</b> , 30, 1348-1350		5
43	Recombination kinetics and intersubband relaxation in semiconductor quantum wires. <i>Semiconductor Science and Technology</i> , <b>1994</b> , 9, 1939-1945	1.8	35
42	Pseudomorphic quantum wires: Symmetry breaking due to structural, strain and piezoelectric field induced confinement. <i>Superlattices and Microstructures</i> , <b>1994</b> , 16, 249-251	2.8	2
41	Radiative recombination in pseudomorphic InGaAs/GaAs quantum wires grown on nonplanar substrates. <i>Solid-State Electronics</i> , <b>1994</b> , 37, 1097-1100	1.7	10

40	Strain distribution in InP grown on patterned Si: Direct visualization by cathodoluminescence wavelength imaging. <i>Journal of Electronic Materials</i> , <b>1994</b> , 23, 201-206	1.9	9
39	Low threshold, large To injection laser emission from (InGa)As quantum dots. <i>Electronics Letters</i> , <b>1994</b> , 30, 1416-1417	1.1	662
38	Symmetry breaking in pseudomorphic V-groove quantum wires. <i>Physical Review B</i> , <b>1994</b> , 50, 14187-14193	3.3	59
37	Epitaxy of high resistivity InP on Si. <i>Applied Physics Letters</i> , <b>1993</b> , 63, 3607-3609	3.4	2
36	Carrier Capture and Stimulated Emission in Quantum Wire Lasers Grown on Nonplanar Substrates <b>1993</b> , 317-330		3
35	Maskless growth of InP stripes on patterned Si (001): Defect reduction and improvement of optical properties. <i>Applied Physics Letters</i> , <b>1992</b> , 60, 3292-3294	3.4	10
34	InGaAs/InP quantum wells on vicinal Si(001): Structural and optical properties. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1992</b> , 10, 1840		2
33	Nonspectroscopic approach to the determination of the chemical potential and band-gap renormalization in quantum wells. <i>Physical Review B</i> , <b>1992</b> , 45, 8535-8541	3.3	6
32	Interfacial properties of very thin GaInAs/InP quantum well structures grown by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>1992</b> , 71, 3300-3306	2.5	50
31	Ultrafast carrier capture and long recombination lifetimes in GaAs quantum wires grown on nonplanar substrates. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 67-69	3.4	66
30	Crystallographic and optical properties of InP/Si(001) grown by low temperature MOCVD process. <i>Surface Science</i> , <b>1992</b> , 267, 47-49	1.8	5
29	Cathodoluminescence investigation of lateral carrier confinement in GaAs/AlGaAs quantum wires grown by OMCVD on nonplanar substrates. <i>Surface Science</i> , <b>1992</b> , 267, 257-262	1.8	31
28	1D Charge Carrier Dynamics in GaAs Quantum Wires Carrier Capture, Relaxation, and Recombination. <i>Physica Status Solidi (B): Basic Research</i> , <b>1992</b> , 173, 307-321	1.3	17
27	Quantum wire heterostructure for optoelectronic applications. <i>Superlattices and Microstructures</i> , <b>1992</b> , 12, 491-499	2.8	44
26	InP on patterned Si(001): defect reduction by application of the necking mechanism. <i>Journal of Crystal Growth</i> , <b>1992</b> , 124, 207-212	1.6	11
25	Cathodoluminescence of strained quantum wells and layers. <i>Superlattices and Microstructures</i> , <b>1991</b> , 9, 65-75	2.8	3
24	Corrosion and mechanical properties of the martensitic steel X18CrMoVNb 12 1 in flowing Pb?17Li. <i>Fusion Engineering and Design</i> , <b>1991</b> , 14, 329-334	1.7	15
23	LP-MOVPE growth of antiphase domain free InP on (001) Si using low temperature processing. <i>Journal of Crystal Growth</i> , <b>1991</b> , 107, 494-495	1.6	4

22	Determination of the band discontinuity of MOCVD grown $\text{In}_{1-x}\text{Ga}_x\text{As}/\text{In}_{1-y}\text{Al}_y\text{As}$ heterostructures with optical and structural methods. <i>Journal of Crystal Growth</i> , <b>1991</b> , 107, 555-560	1.6	6
21	Antiphase-domain-free InP on Si(001): optimization of MOCVD process. <i>Journal of Crystal Growth</i> , <b>1991</b> , 115, 150-153	1.6	9
20	Direct imaging of Si incorporation in GaAs masklessly grown on patterned Si substrates. <i>Applied Physics Letters</i> , <b>1991</b> , 58, 2090-2092	3.4	11
19	Low-temperature metalorganic chemical vapor deposition of InP on Si(001). <i>Applied Physics Letters</i> , <b>1991</b> , 58, 284-286	3.4	88
18	Scanning cathodoluminescence microscopy: A unique approach to atomic-scale characterization of heterointerfaces and imaging of semiconductor inhomogeneities. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1991</b> , 9, 2259		148
17	Observation of the first-order phase transition from single to double stepped Si (001) in metalorganic chemical vapor deposition of InP on Si. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1991</b> , 9, 2156		20
16	Direct imaging and theoretical modelling of the atomistic morphological and chemical structure of semiconductor heterointerfaces. <i>Applied Surface Science</i> , <b>1990</b> , 41-42, 329-336	6.7	13
15	Dependence of structural and optical properties of $\text{In}_{0.23}\text{Ga}_{0.77}\text{As}/\text{GaAs}$ quantum wells on misfit dislocations: Different critical thickness for dislocation generation and degradation of optical properties. <i>Journal of Vacuum Science &amp; Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , <b>1990</b> , 8, 751		40
14	Recombination dynamics in pseudomorphic and partially relaxed $\text{In}_{0.23}\text{Ga}_{0.77}\text{As}/\text{GaAs}$ quantum wells. <i>Physical Review B</i> , <b>1990</b> , 41, 10120-10123	3.3	16
13	Image charges in semiconductor quantum wells: Effect on exciton binding energy. <i>Physical Review B</i> , <b>1990</b> , 42, 5906-5909	3.3	131
12	Pseudomorphic $\text{In}_{0.23}\text{Ga}_{0.77}\text{As}/\text{GaAs}$ Quantum Wells: Correlation of Anisotropic Lattice Relaxation and Degradation of Optical Properties. <i>Springer Series in Solid-state Sciences</i> , <b>1990</b> , 304-312	0.4	
11	Anisotropic and inhomogeneous strain relaxation in pseudomorphic $\text{In}_{0.23}\text{Ga}_{0.77}\text{As}/\text{GaAs}$ quantum wells. <i>Applied Physics Letters</i> , <b>1989</b> , 55, 1765-1767	3.4	62
10	Genome type analysis of adenoviruses: isolates from one year from the Hannover area. <i>Archives of Virology</i> , <b>1989</b> , 105, 89-101	2.6	14
9	Misfit dislocations in pseudomorphic $\text{In}_{0.23}\text{Ga}_{0.77}\text{As}/\text{GaAs}$ quantum wells: Influence on lifetime and diffusion of excess excitons. <i>Journal of Applied Physics</i> , <b>1989</b> , 66, 2214-2216	2.5	26
8	A vanadium alloy for the application in a liquid metal blanket of a fusion reactor. <i>Journal of Nuclear Materials</i> , <b>1988</b> , 155-157, 690-693	3.3	19
7	The influence of liquid $\text{Pb}_{17}\text{Li}$ eutectic on the mechanical properties of structural materials. <i>Fusion Engineering and Design</i> , <b>1988</b> , 6, 155-158	1.7	6
6	Anisotropy effects on excitonic properties in realistic quantum wells. <i>Physical Review B</i> , <b>1988</b> , 38, 13486-13489	3.3	77
5	The fracture of austenitic and martensitic steel in liquid lithium. <i>Nuclear Engineering and Design/fusion: an International Journal Devoted To the Thermal, Mechanical, Materials, Structural, and Design Problems of Fusion Energy</i> , <b>1986</b> , 3, 273-286		6



4	Studies of Corrosion and Impact on Mechanical Properties of SS 304 and 12 % CR Steel by Liquid Lithium. <i>Fusion Science and Technology</i> , <b>1985</b> , 8, 536-540	3
3	Edge and surface emitting quantum dot lasers	1
2	Static and dynamic properties of (InGa)As/GaAs quantum dot lasers	1
1	Strain states and relaxation for $(\alpha)\text{-}(\text{Al}_x\text{Ga}_{1-x})_2\text{O}_3$ thin films on prismatic planes of $(\alpha)\text{-Al}_2\text{O}_3$ in the full composition range: Fundamental difference of a- and m-epitaxial planes in the manifestation of shear strain and lattice tilt. <i>Journal of Materials Research</i> , 1	2.5 1